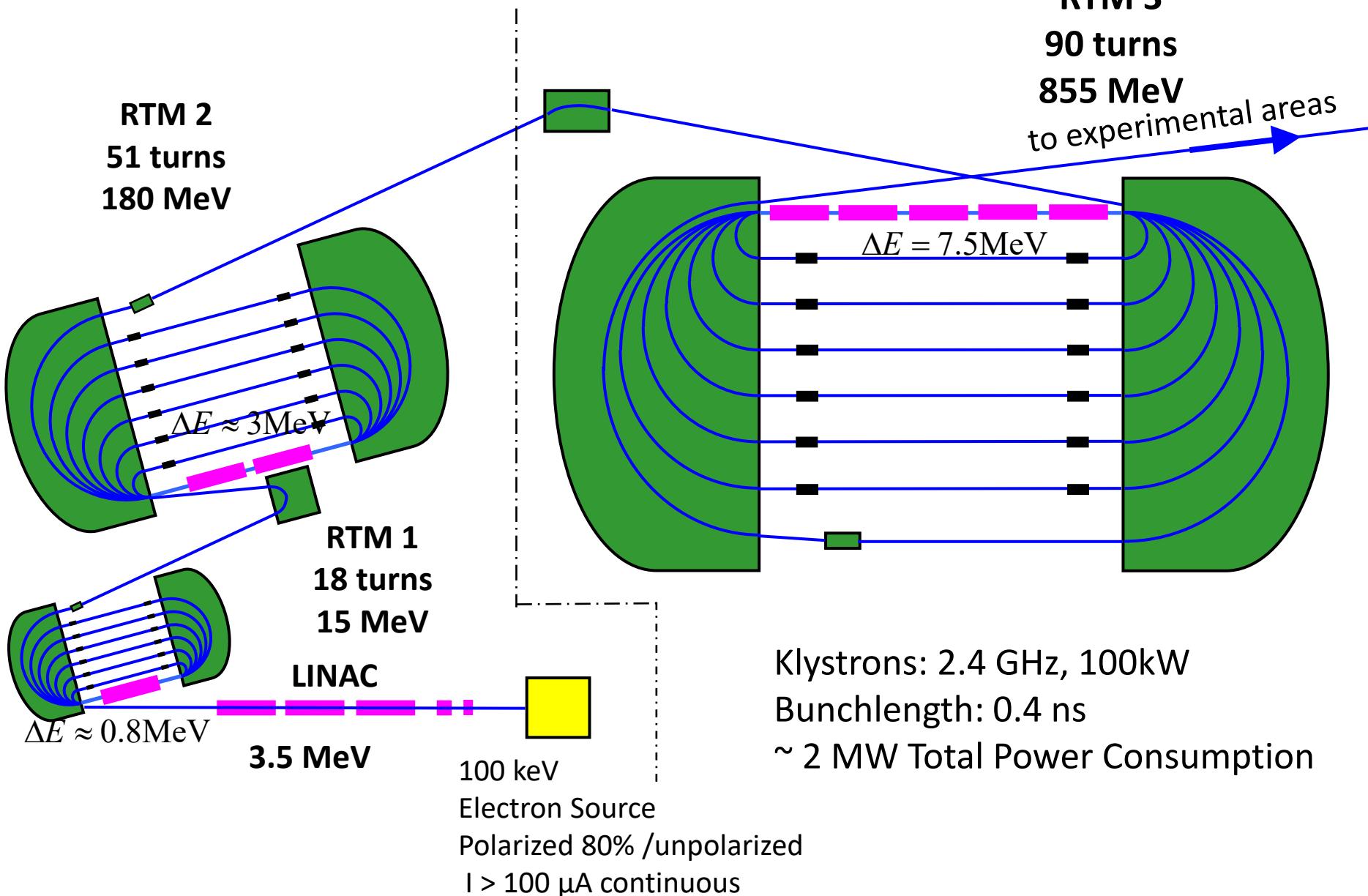


A 530 MeV positron beam for channeling experiments at the Mainz Microtron MAMI

1. Introduction to MAMI
2. Why Positrons
3. Positron beamline @ MAMI with low Emittance
4. Status and future experiments with Positrons

Mainzer Mikrotron MAMI B





Ground plan of MAMI

$E = 180 \text{ MeV} - 1600 \text{ MeV}$

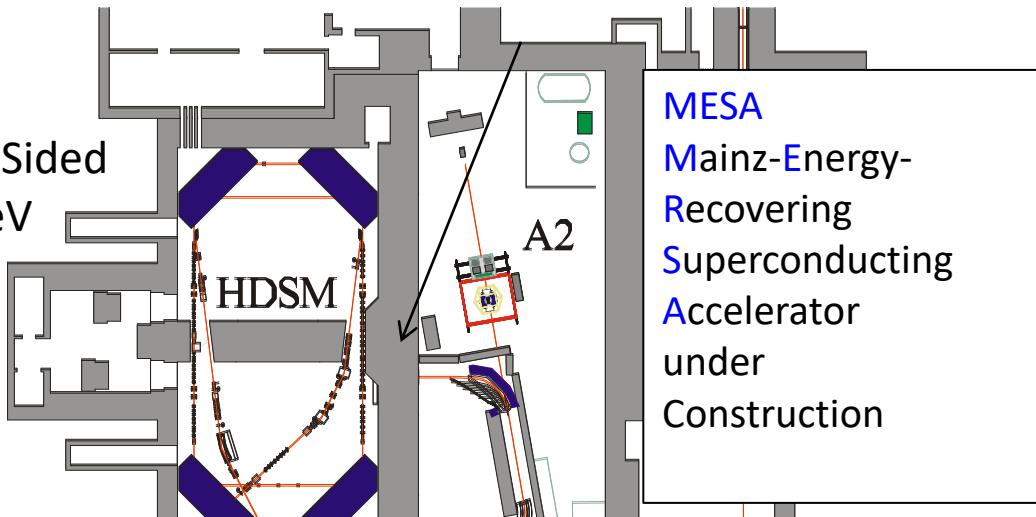
$\Delta E = 13 \text{ keV}$ @ 855 MeV,

$\Delta E/E = (2 \cdot 10^{-5})$

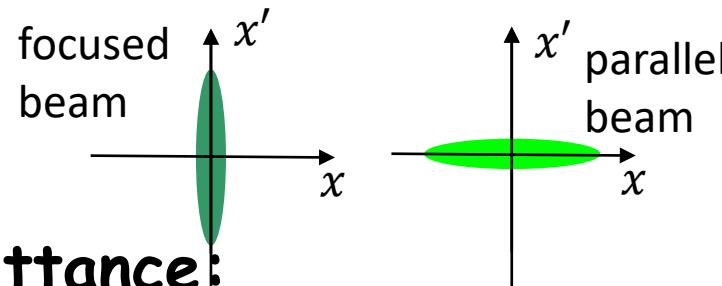
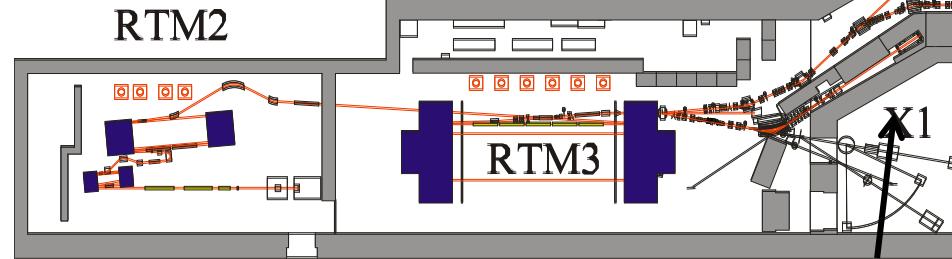
max. $100 \mu\text{A}$ cw e^- - beam

$\sim 7000 \text{ h}$ / year running

Harmonic Double Sided
Microtron: 1.6 GeV



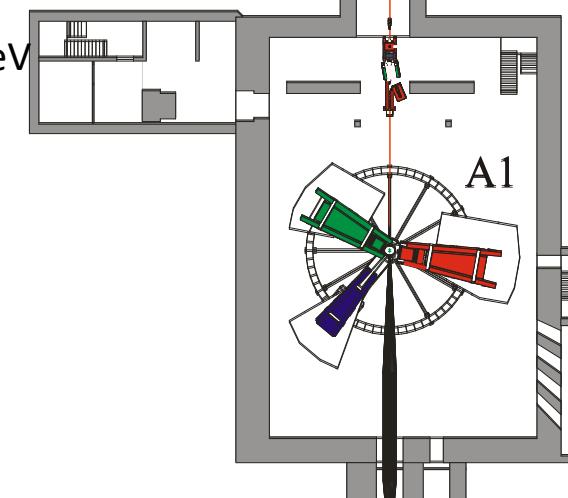
10 m



Emittance:

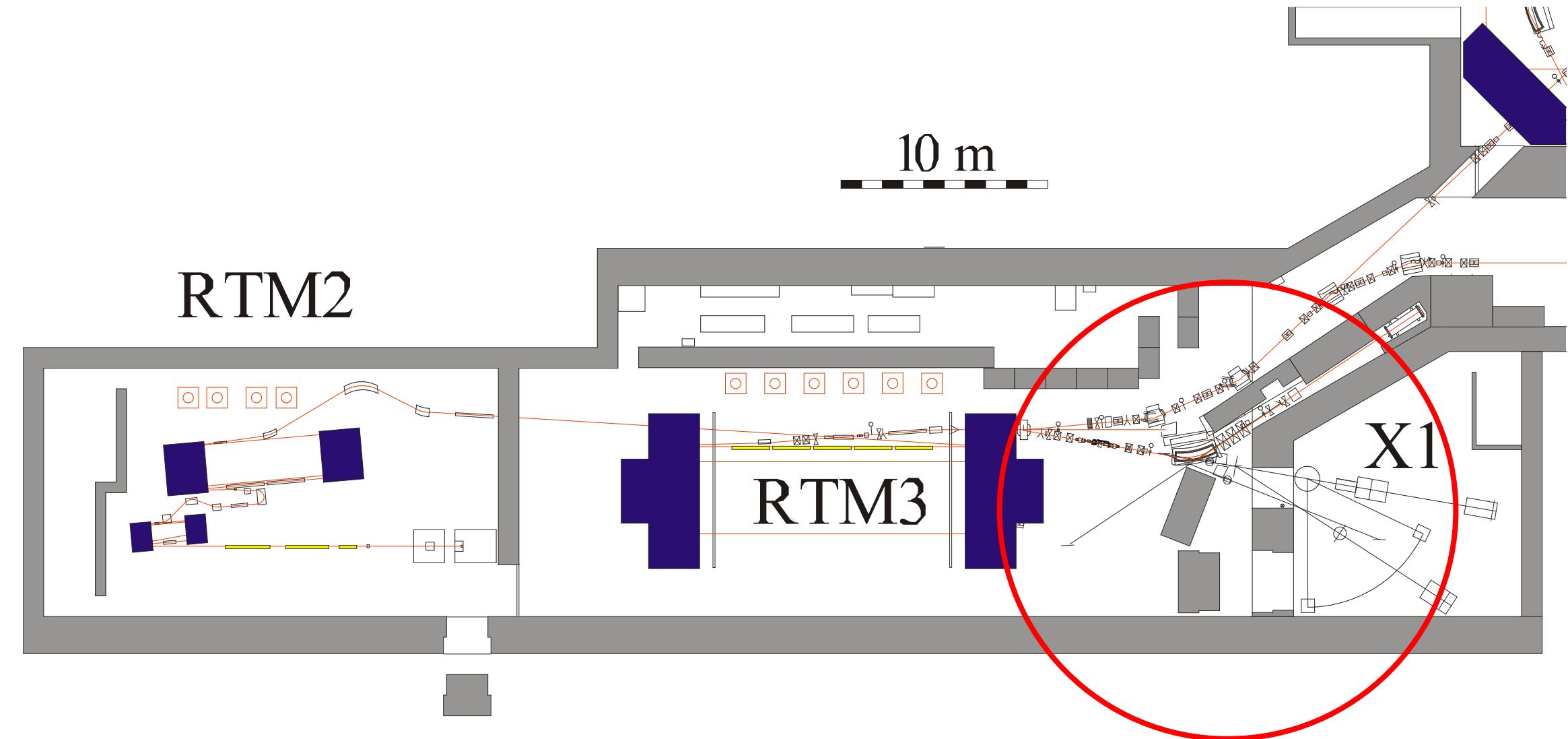
Vertical : $e_y = 1 \mu\text{m mrad} = 1 \text{ mm } \mu\text{rad}$

Horizontal: $e_x = 8 \text{ nm rad}$

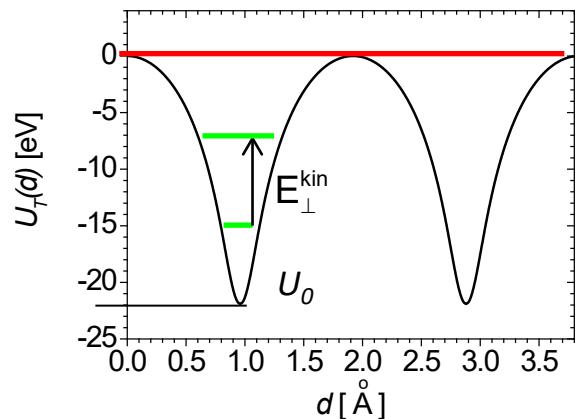
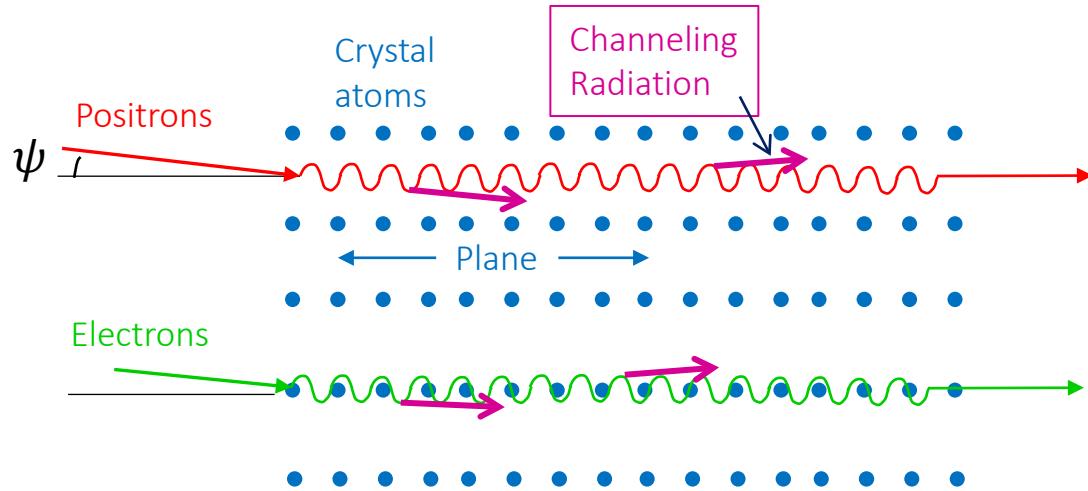


Spectrometer
Hall

Production of high-energy positrons

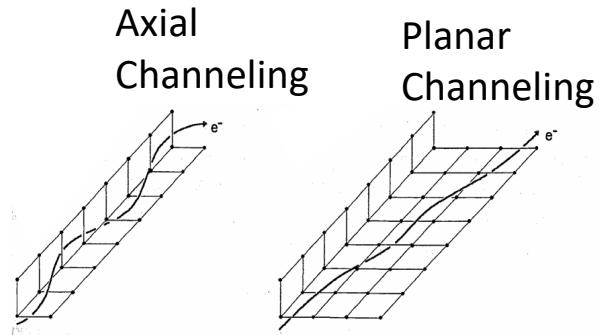


Channeling Radiation



$$E_{\perp}^{\text{kin}} = \frac{p_{\perp}^2 c^2}{2mc^2} \approx \frac{E\psi^2}{2}$$

$$E_{\perp}^{\text{kin}} < U_0 \rightarrow$$



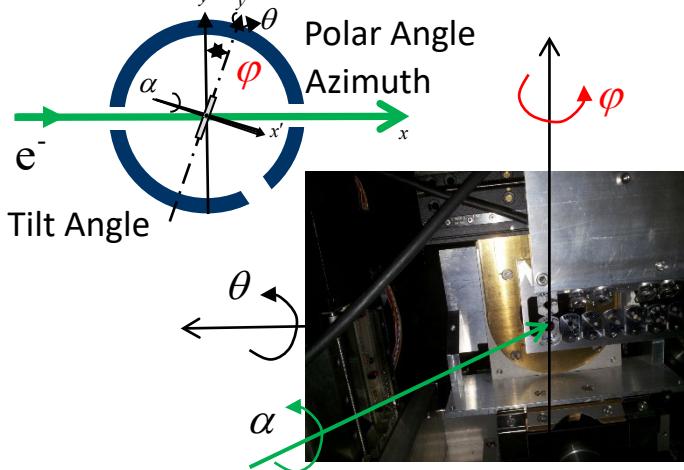
Lindhard
critical angle

$$\psi < \sqrt{\frac{2U_0}{E}} \approx \sqrt{\frac{2 \cdot 20\text{eV}}{1\text{GeV}}}$$

$\psi < 0.2 \text{ mrad}$

Experimental Setup (855) MeV e⁻

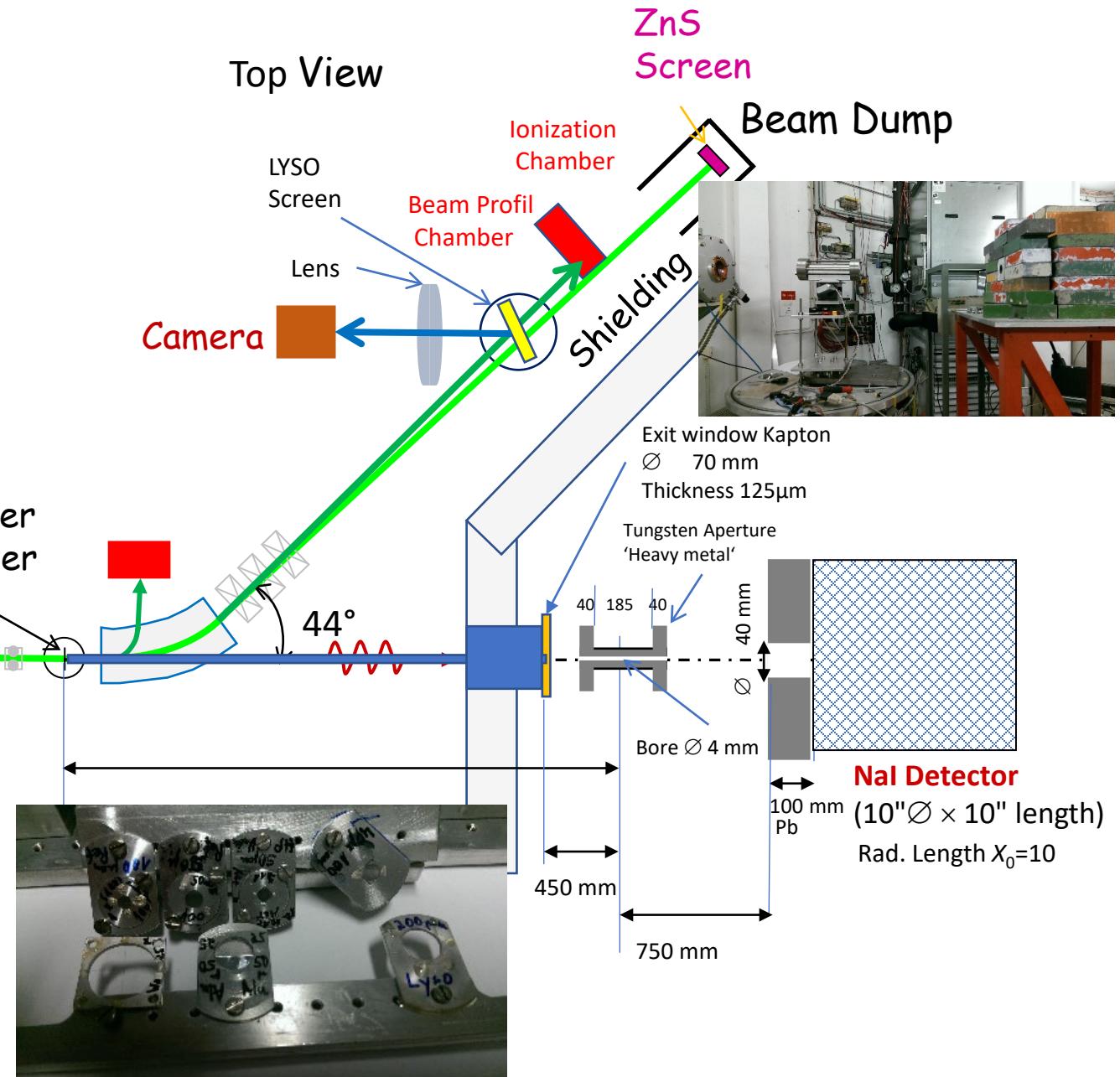
Top View



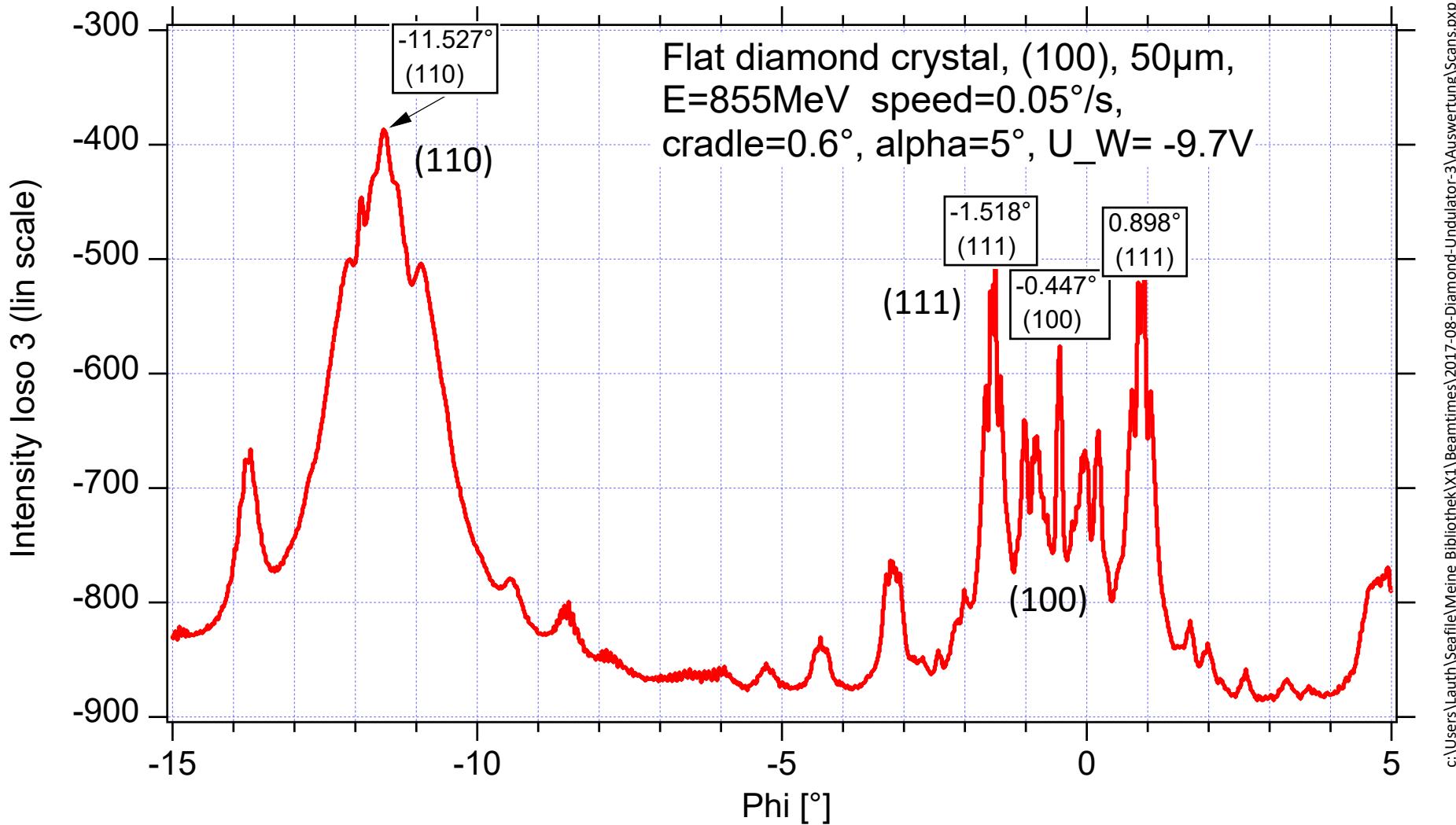
RTM 3

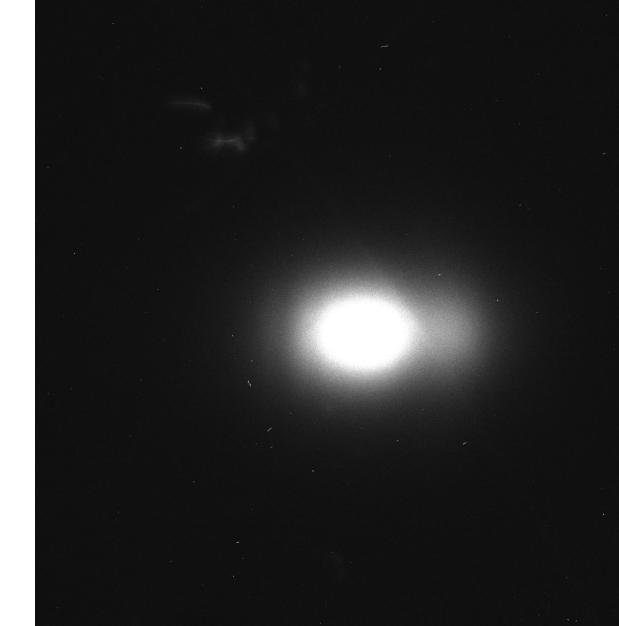
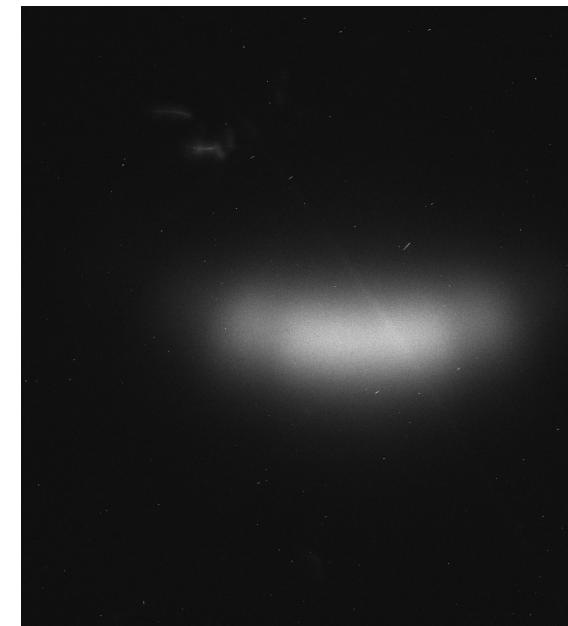
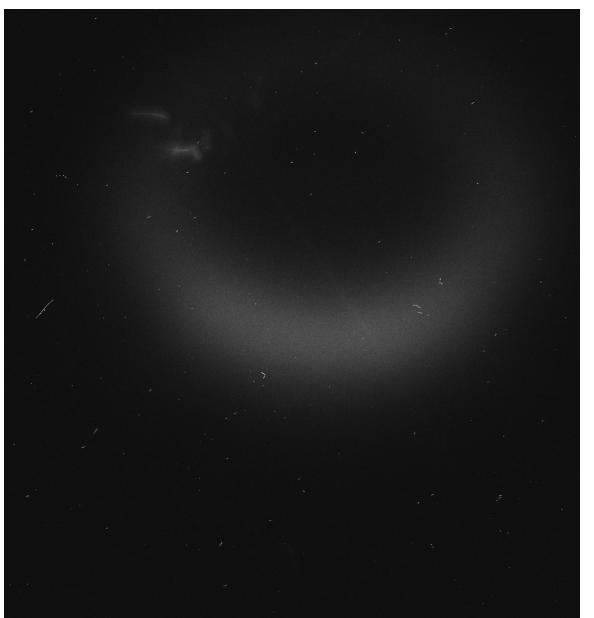
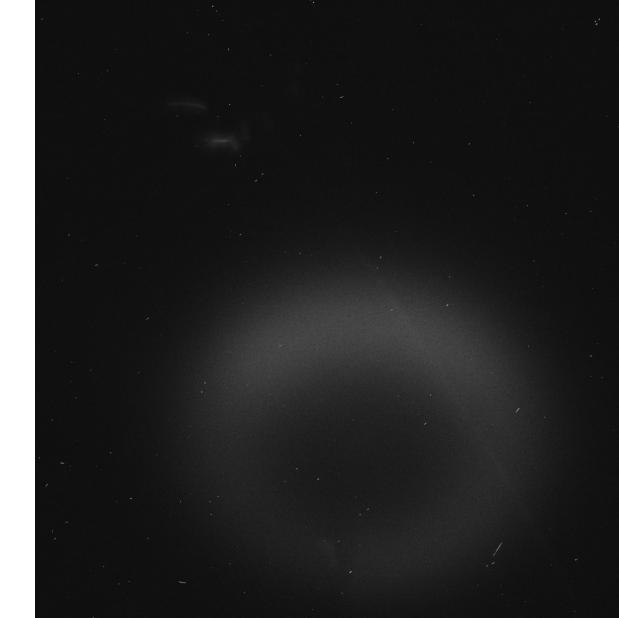
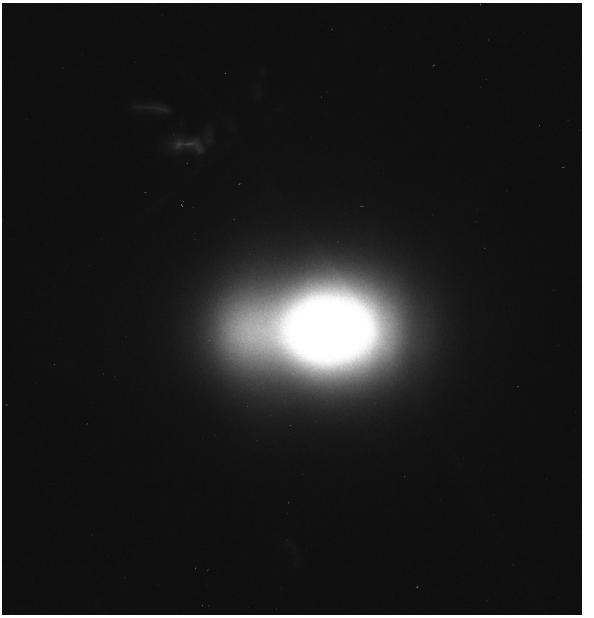
Target Chamber
with Goniometer

Top View

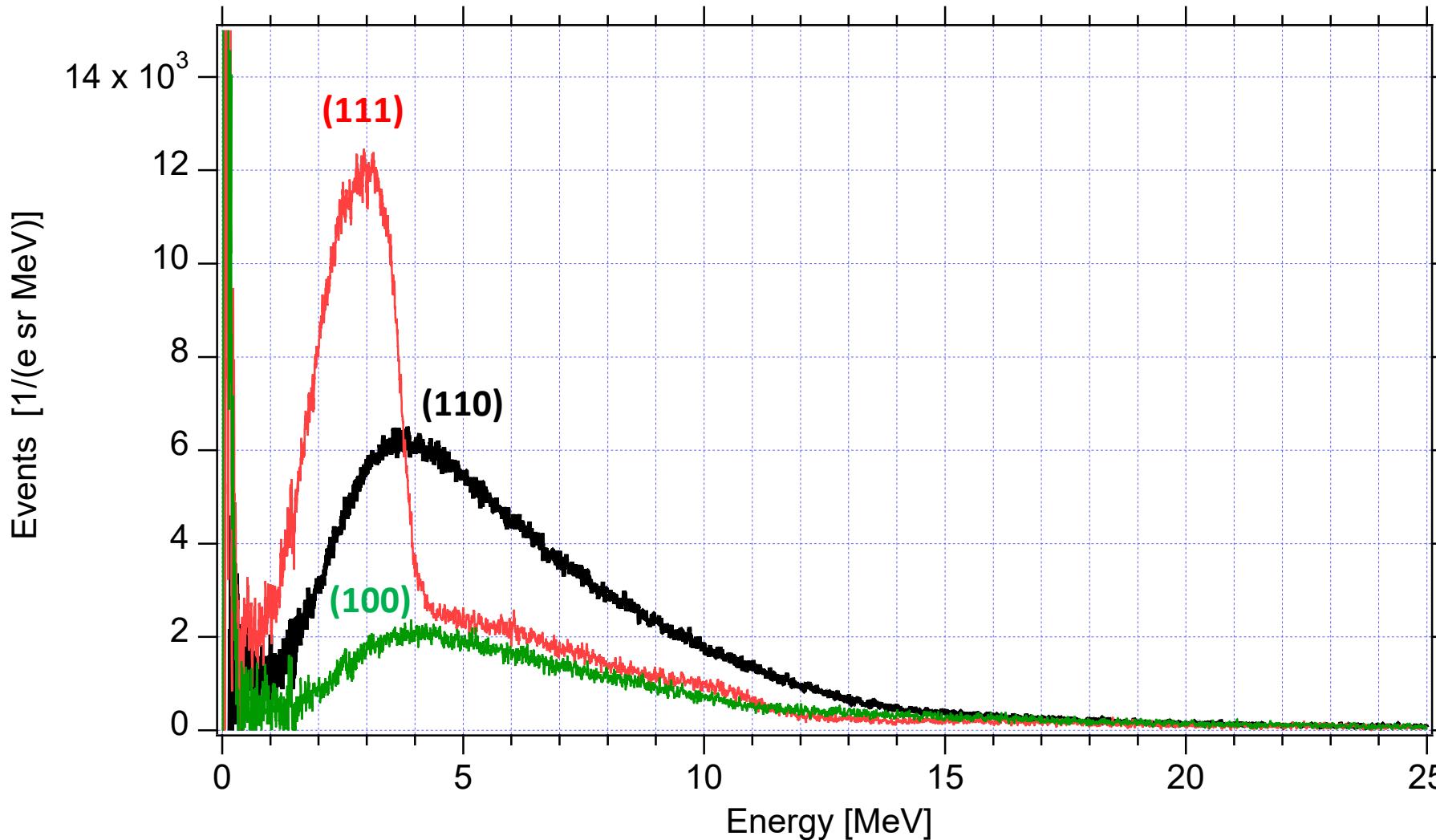


Scan around the vertical axis Φ
Diamond, flat 50 μm crystal
855 MeV e-beam



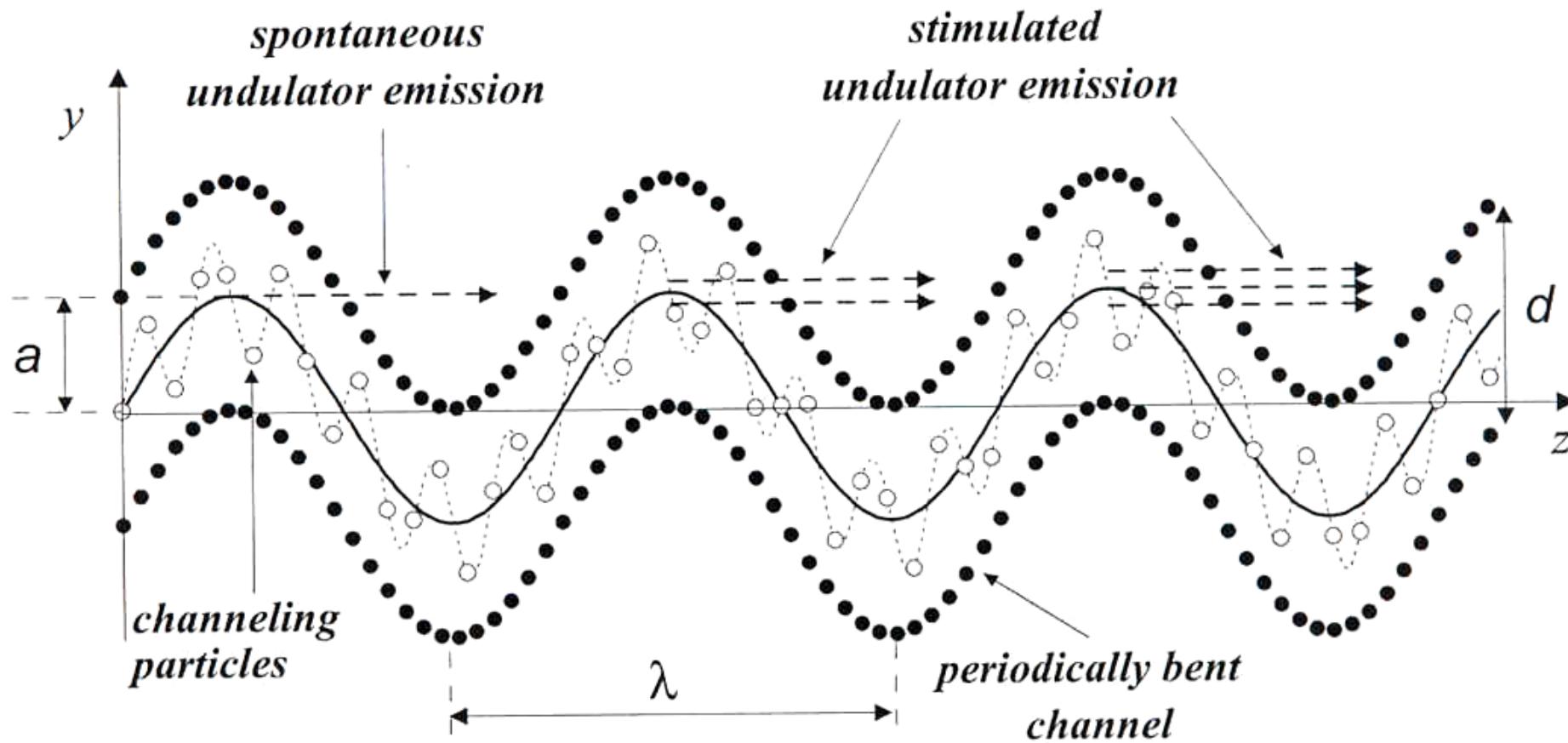


Channeling radiation of a flat diamond crystal



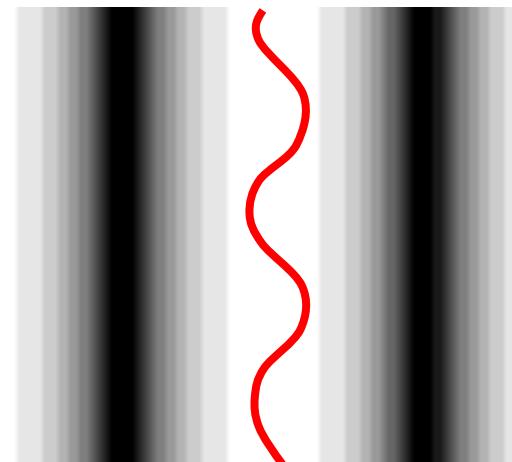
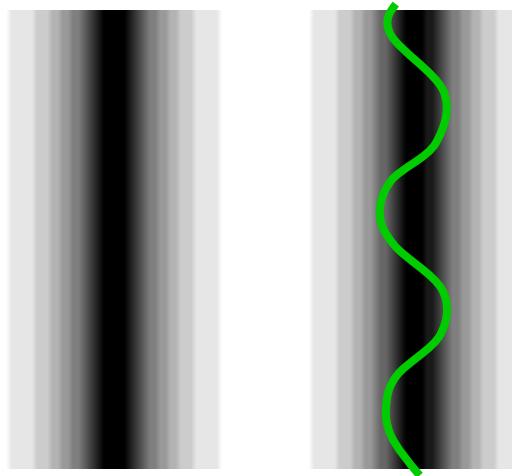
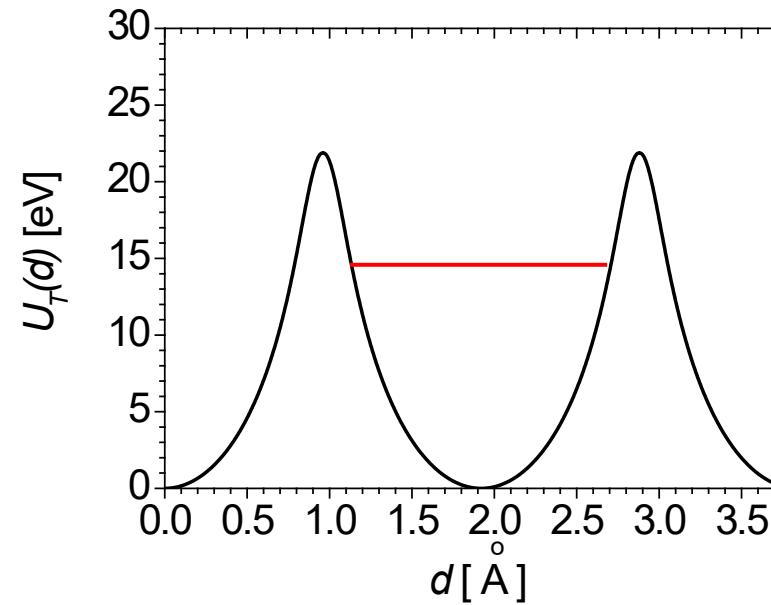
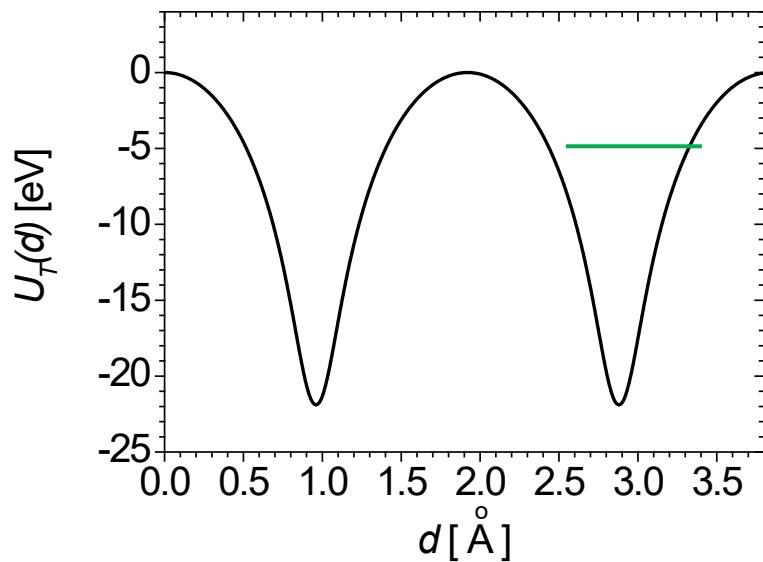
Undulator Radiation at Positron/Electron Channeling in a Single Crystal

A. Solov'yov, A. Korol, W. Greiner *et al.*

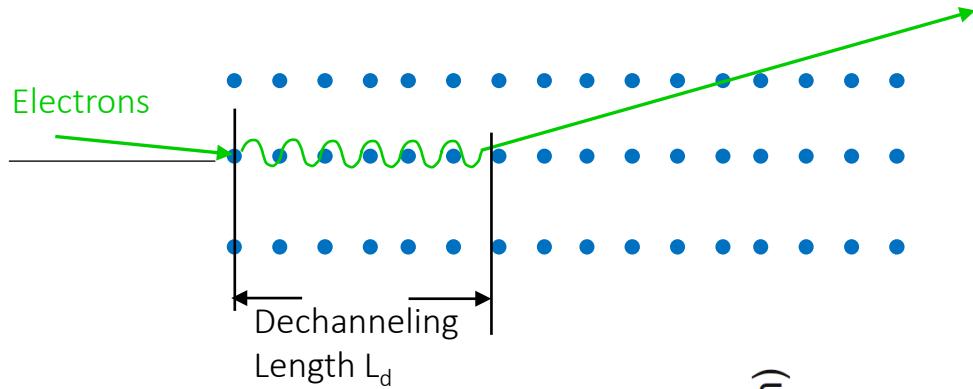


Why Positrons

Electrons versus Positrons

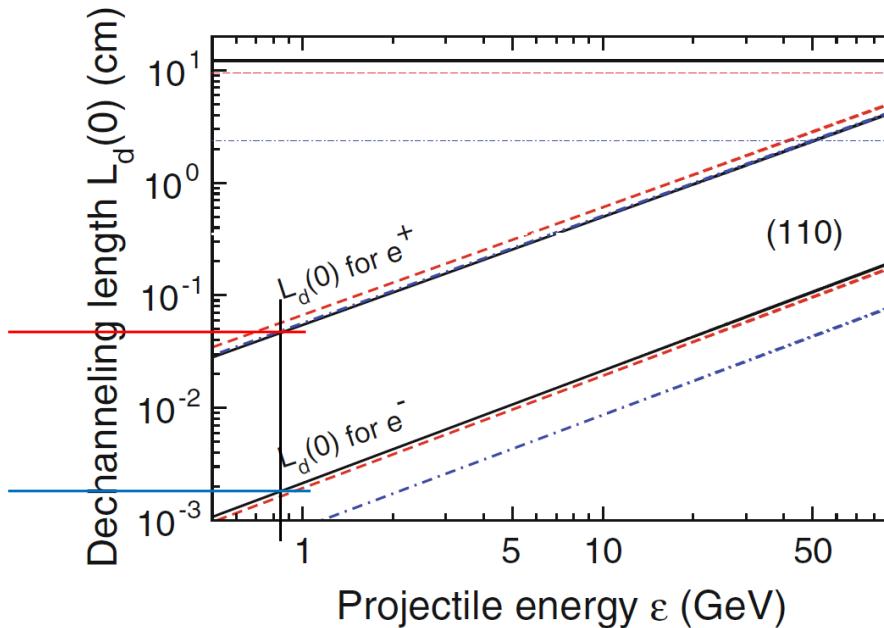


Dechanneling length

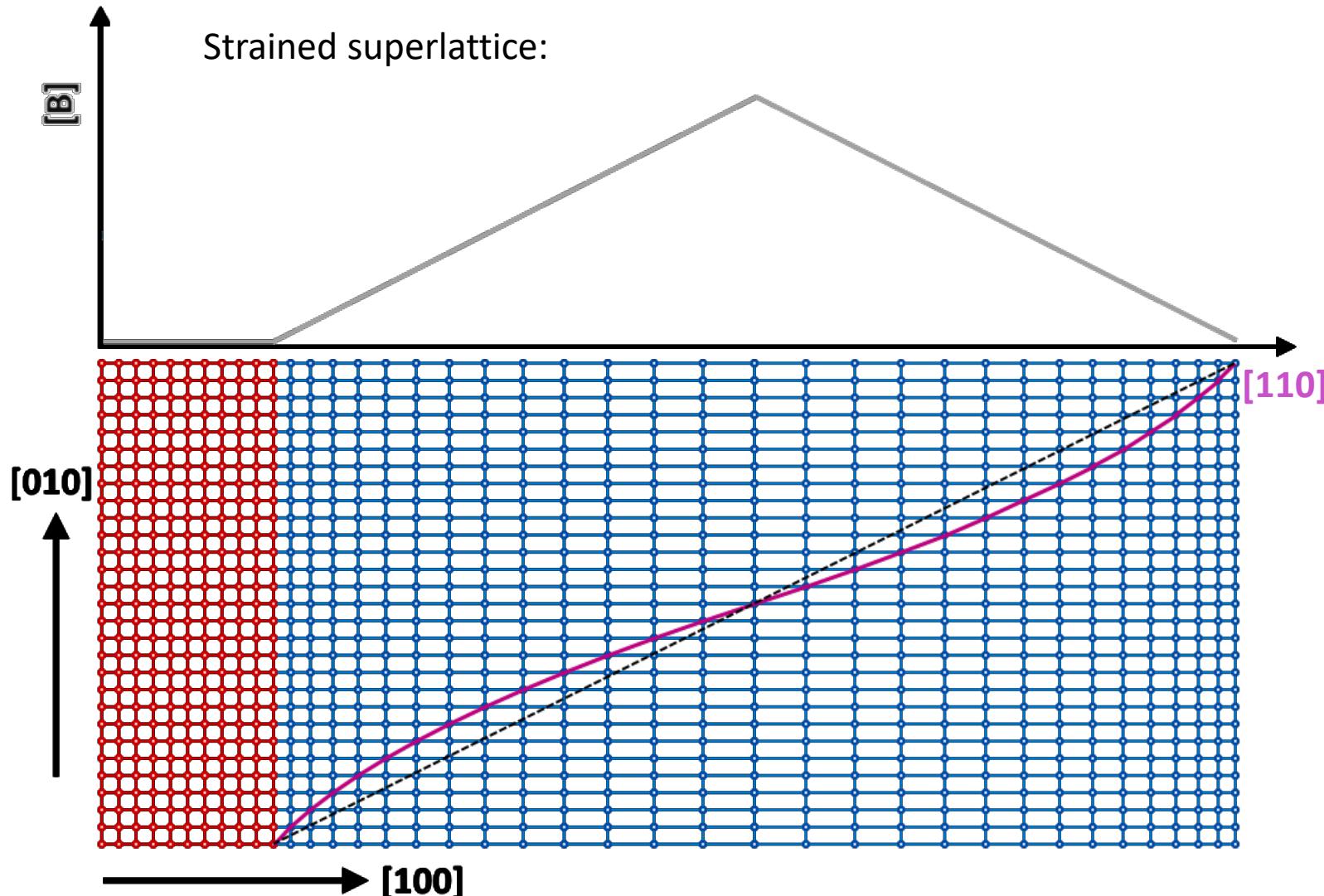


Positrons
~ 300μm

Electrons
~ 20μm
@ 855 MeV



Superlattice principles



Strained superlattice:

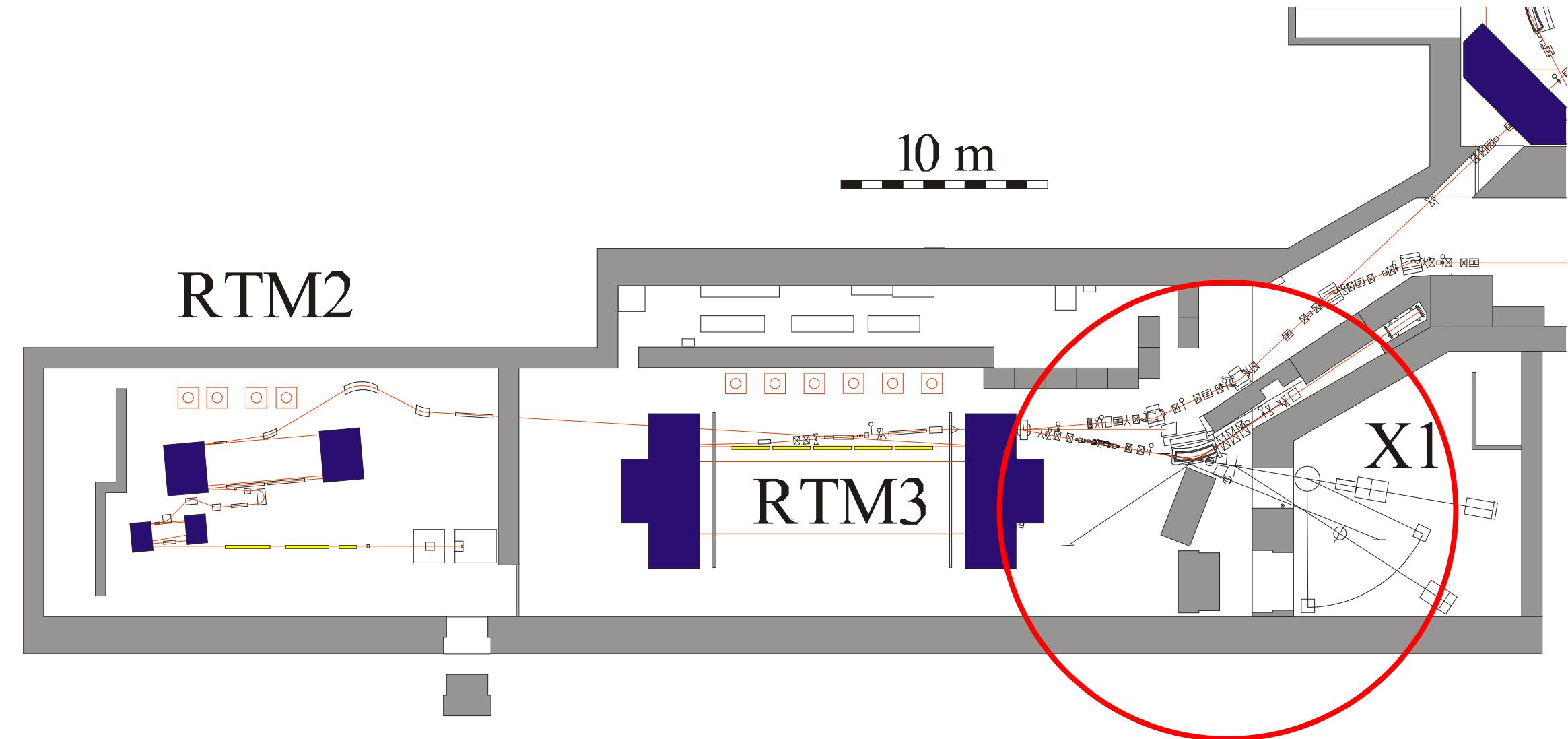
Undoped substrate

Growth with increasing doping
= increase in crystal parameter
along [100].

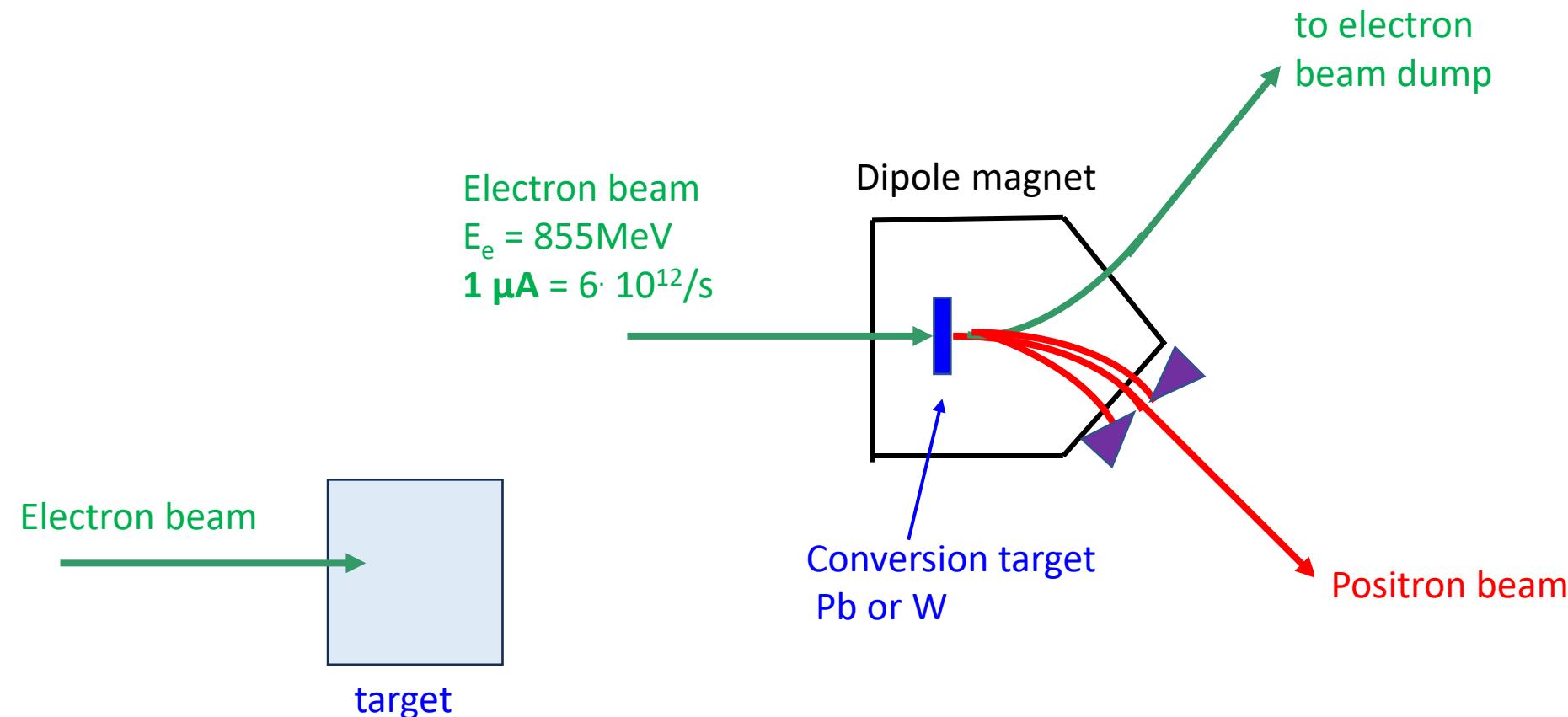
Growth with decreasing doping
= decrease in crystal parameter
along [100]

Channeling along [110]: undulation

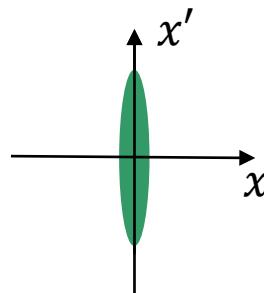
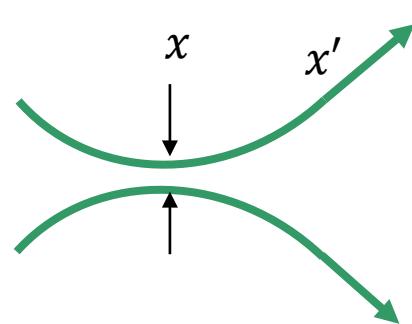
Production of high-energy positrons



Pair production with the MAMI beam in combination with a monochromator



High quality Positron beam @ MAMI



MAMI: $\varepsilon_x = x \cdot x' = 1 \text{ mm} \cdot \mu\text{rad}$
 $= 10 \mu\text{m} \cdot 0.1 \text{ mrad}$

Emittance

$$\varepsilon_x = x \cdot x' = \frac{F}{\pi} = \text{const}$$

Thin target for Positron production

$10 \mu\text{m} W \rightarrow \text{Scattering } \sigma_S = 0.94 \text{ mrad}$

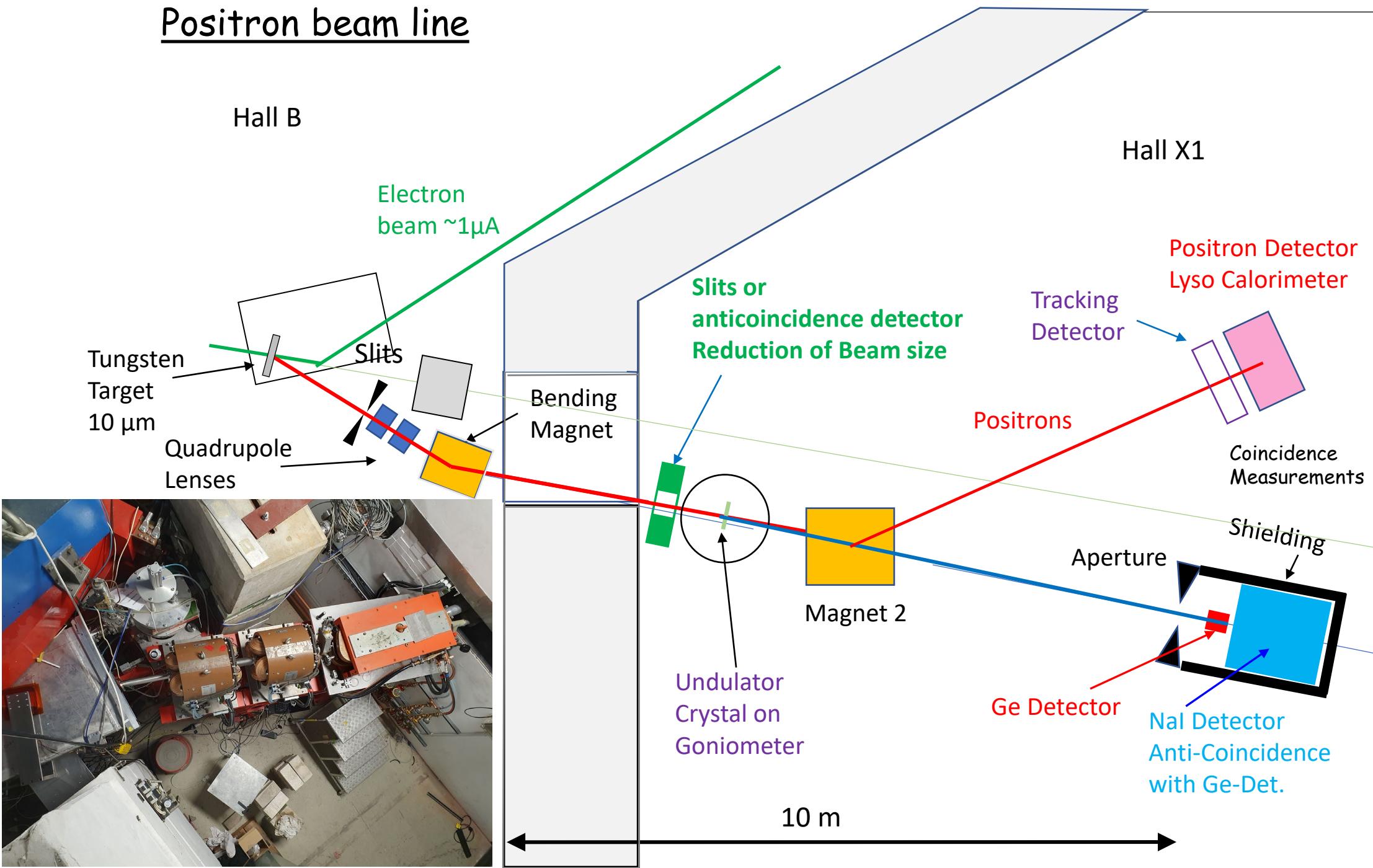
$$\sigma_p \approx \frac{1}{\gamma} = 1 \text{ mrad} @ 500\text{MeV}$$

Emittance of Positrons:

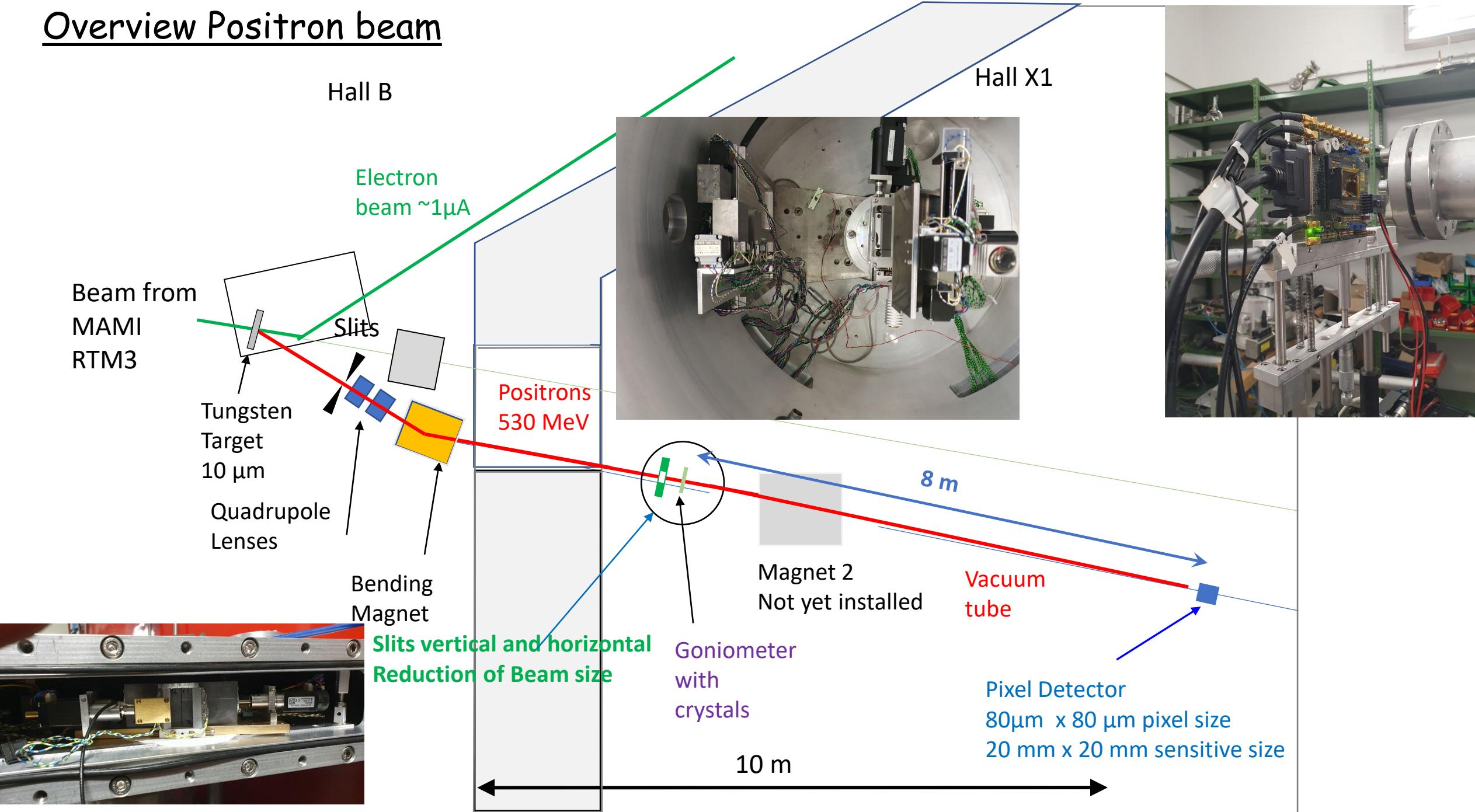
$$\varepsilon_{e+} = 10 \mu\text{m} \cdot 1.4 \text{ mrad}$$

$$= 1 \text{ mm} \cdot 0.014 \text{ mrad}$$

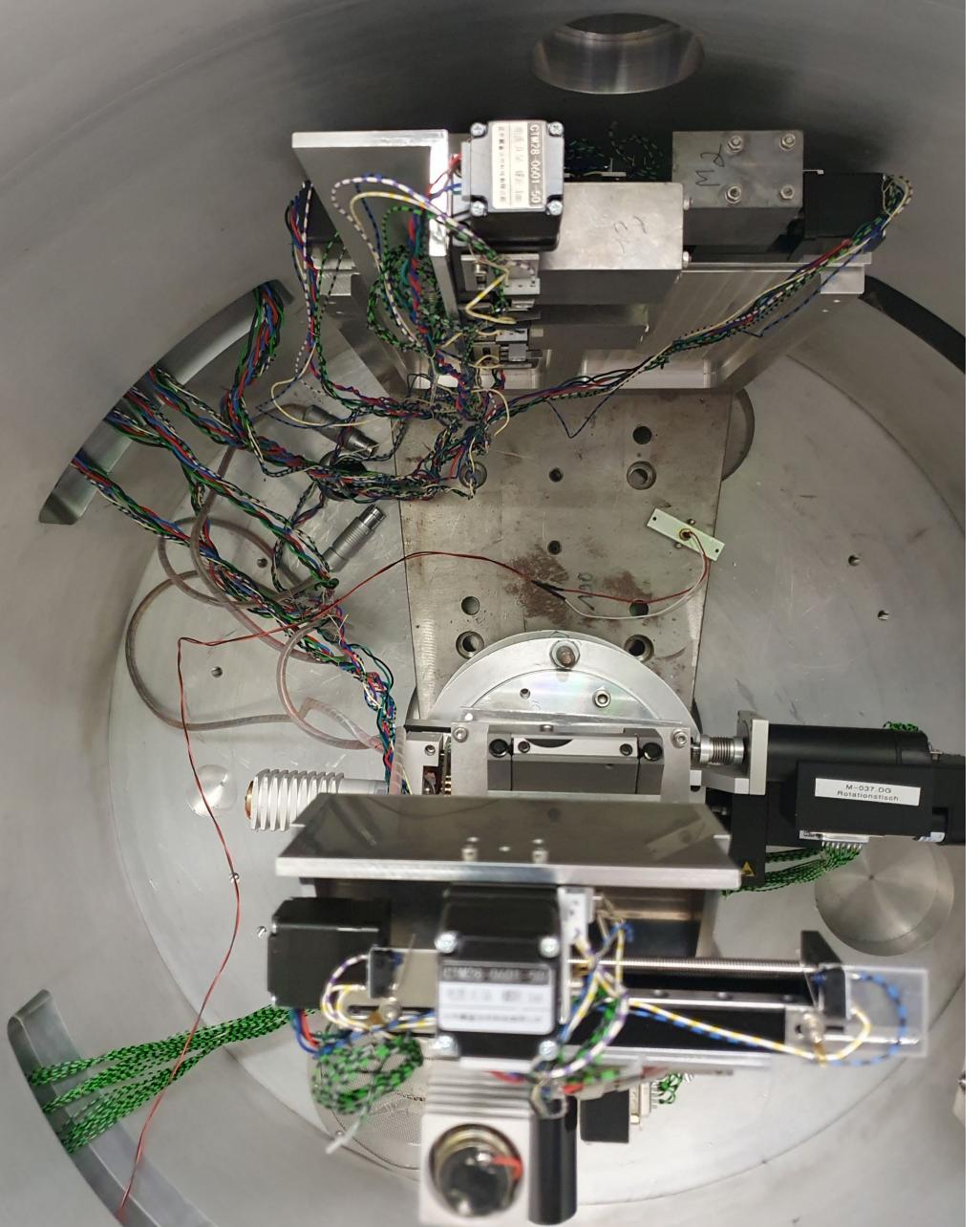
Positron beam line



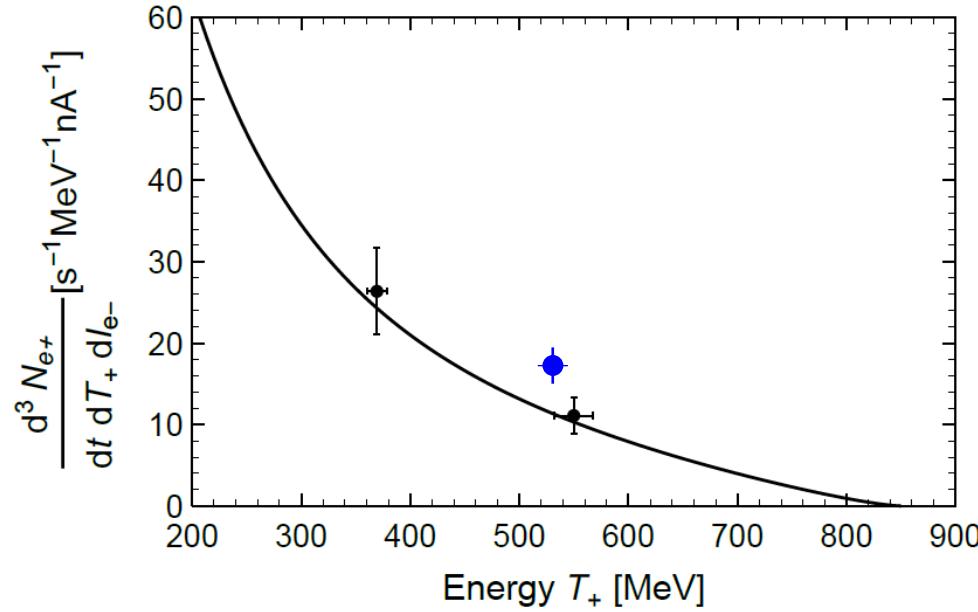
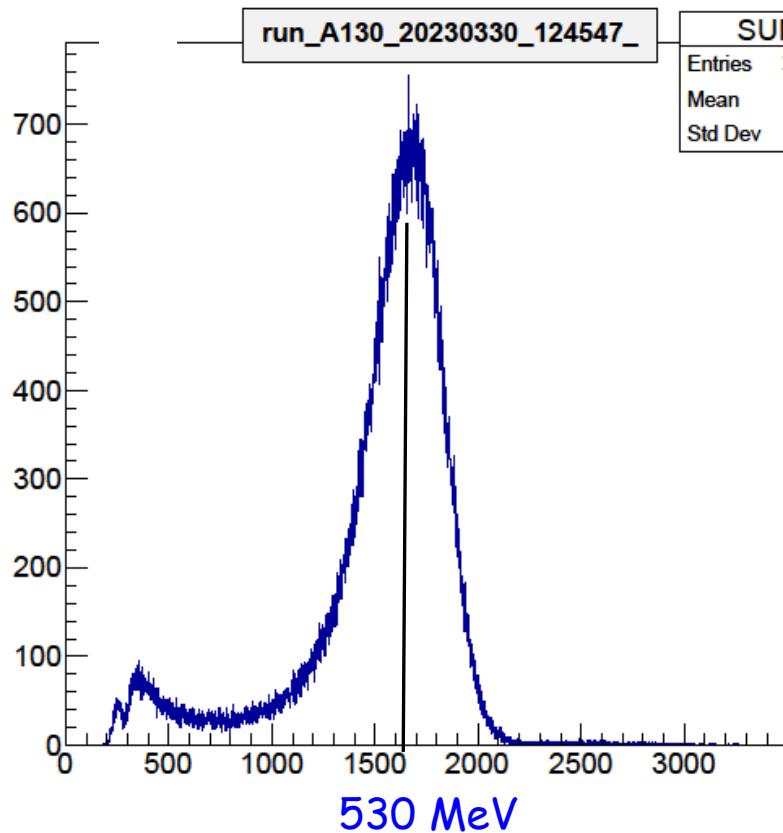
Overview Positron beam







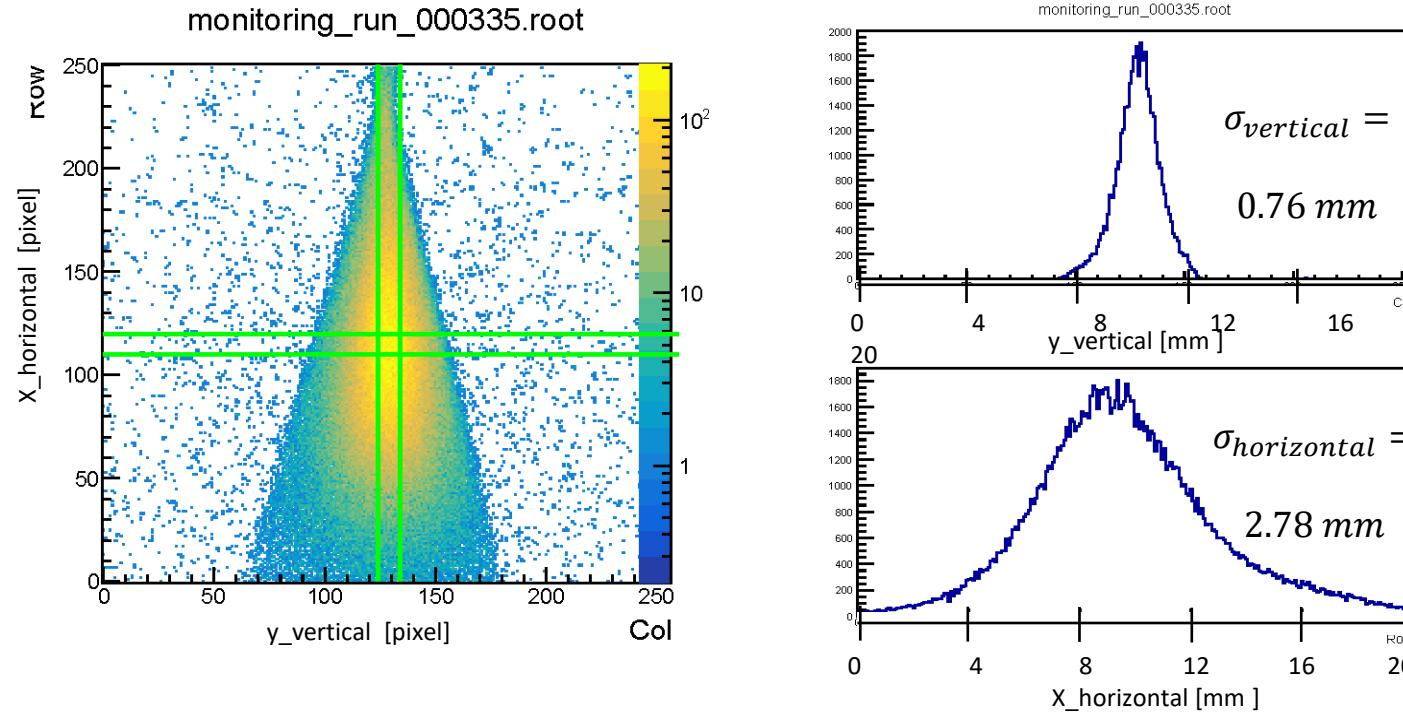
Production Rate



$$17.3 \frac{1}{s \cdot nA \cdot MeV}$$

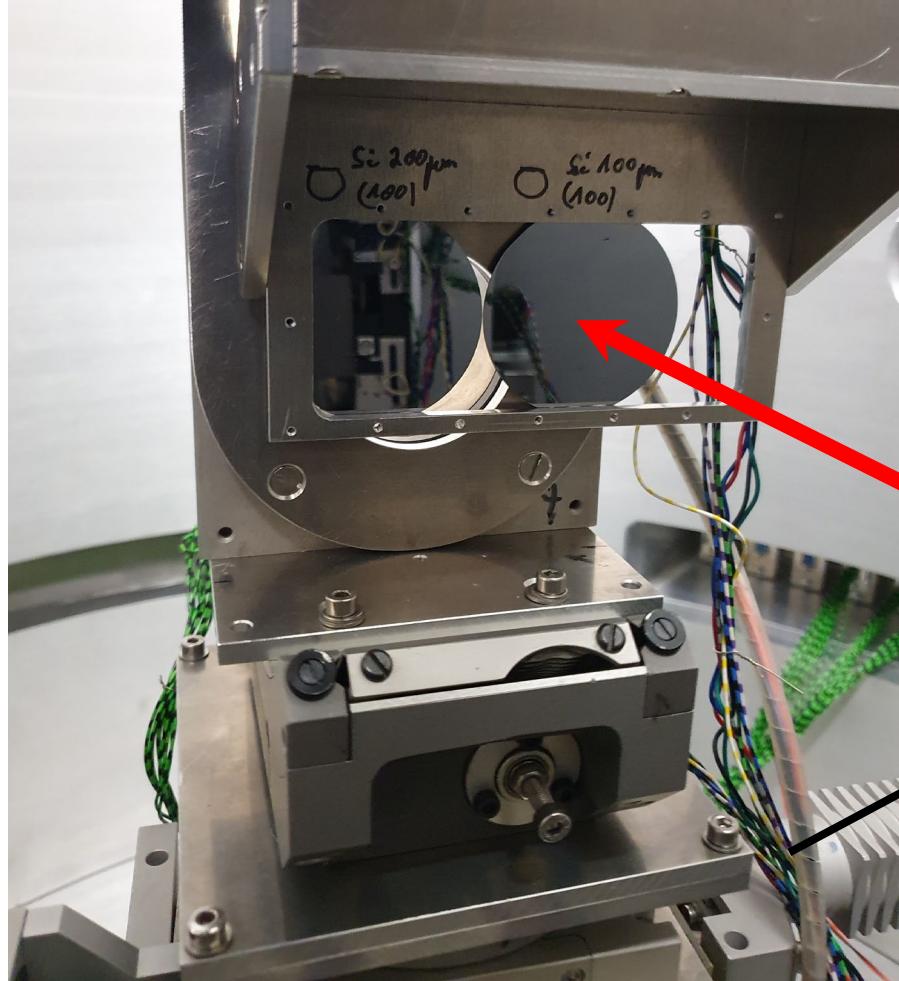
Max. e-current (without shielding) \sim 1 μA ->
Max. positron rate **20 kHz**

Measurement of the beam size of the focused positron beam with the pixel detector



distance of 1.04 m from the centre of the crystal chamber

Channeling of Positrons in Si crystals

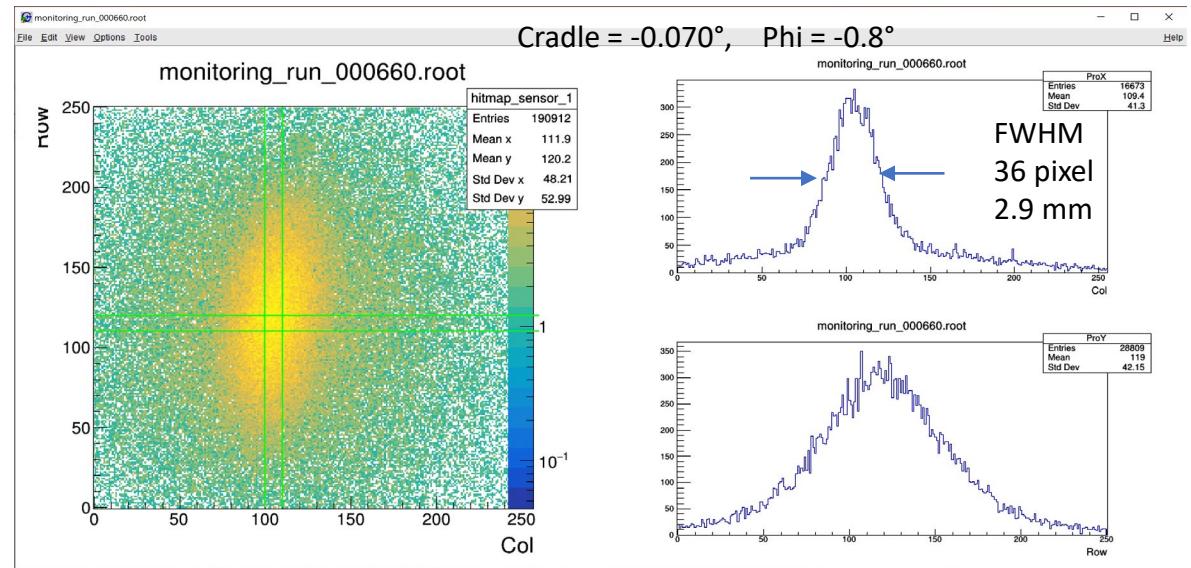
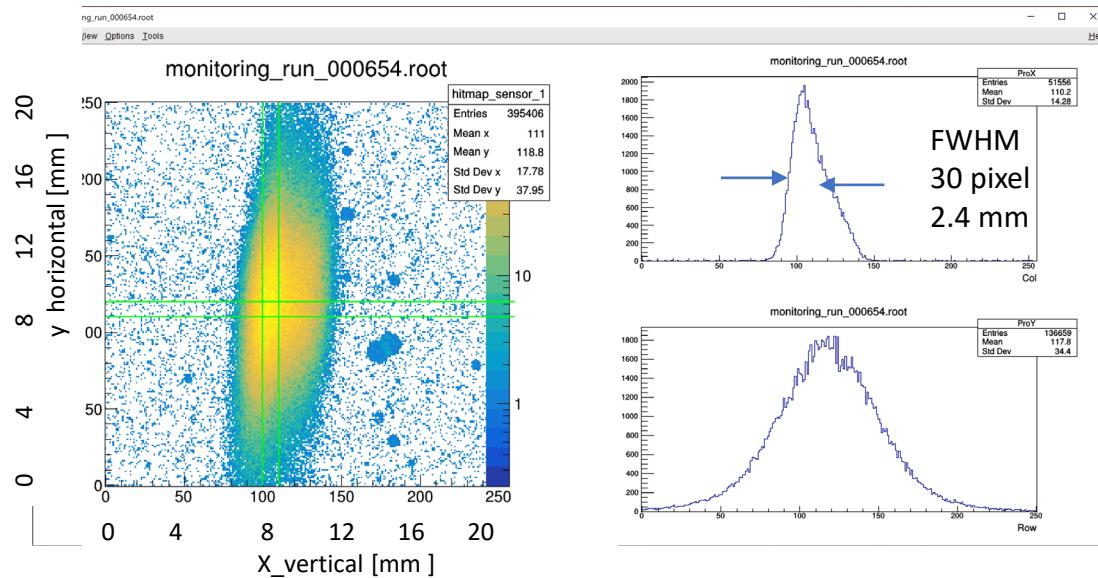


Detection of Positrons with pixel detector

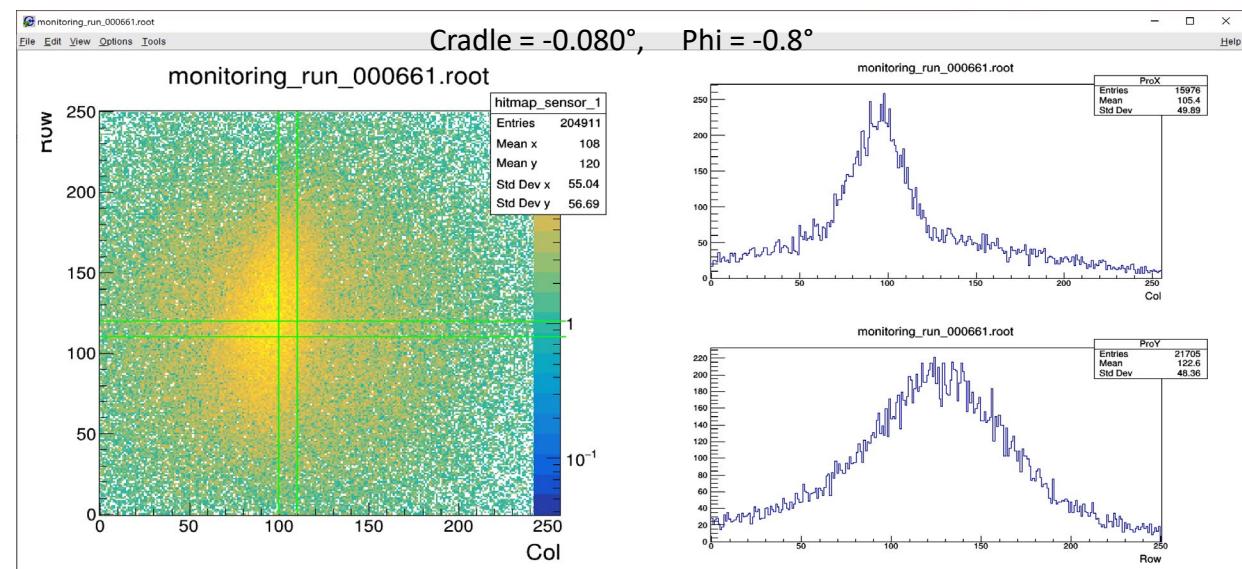
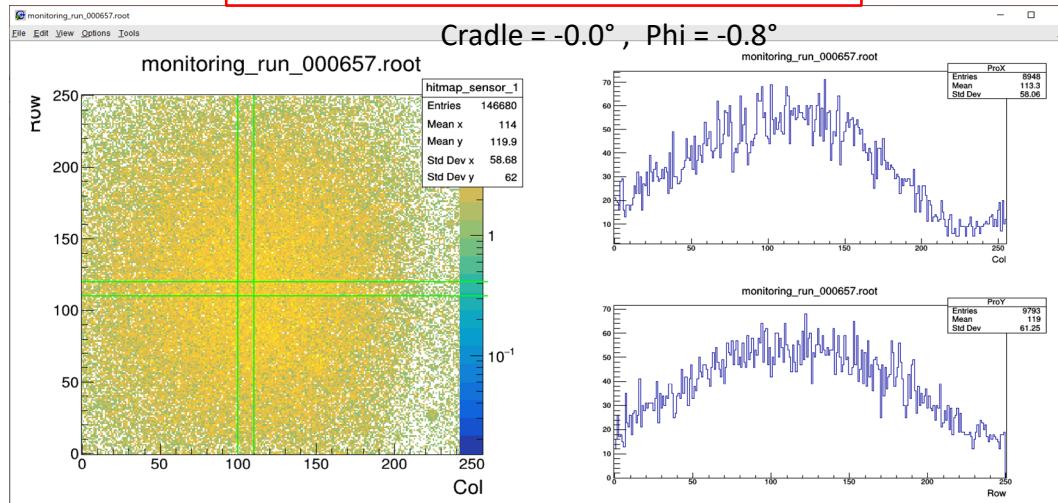
Without crystal

200 μm (100) Si crystal

With oriented crystal

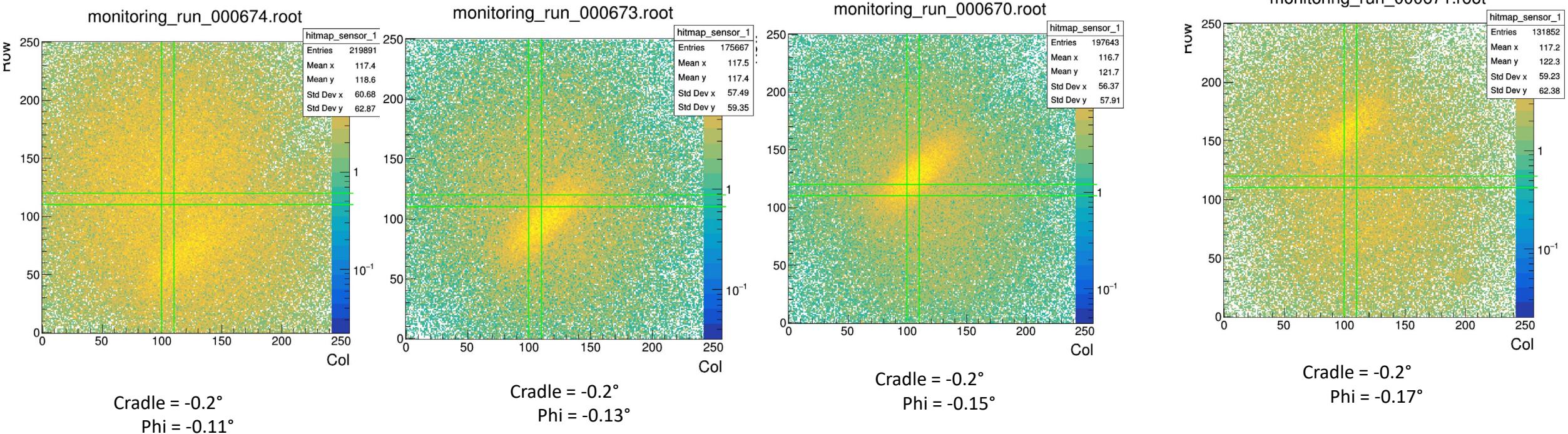


Random orientation of crystal

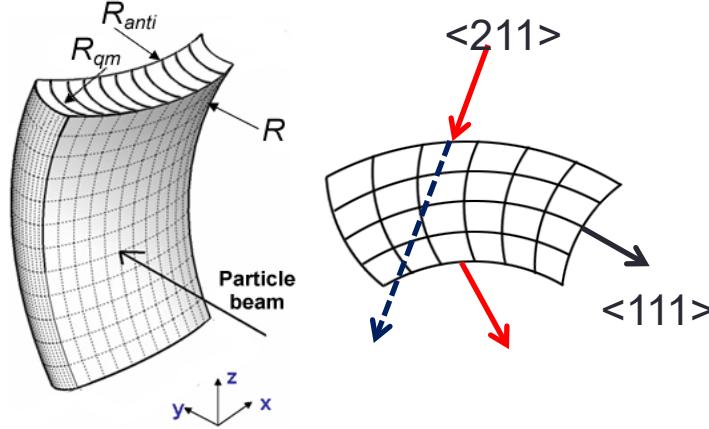


200 μm (100) Si crystal

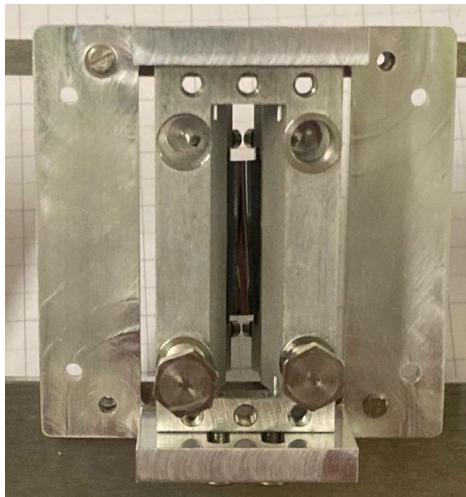
110 Plane Rotation around vertical axis



Mechanically bent Si crystal test with 530 MeV positrons



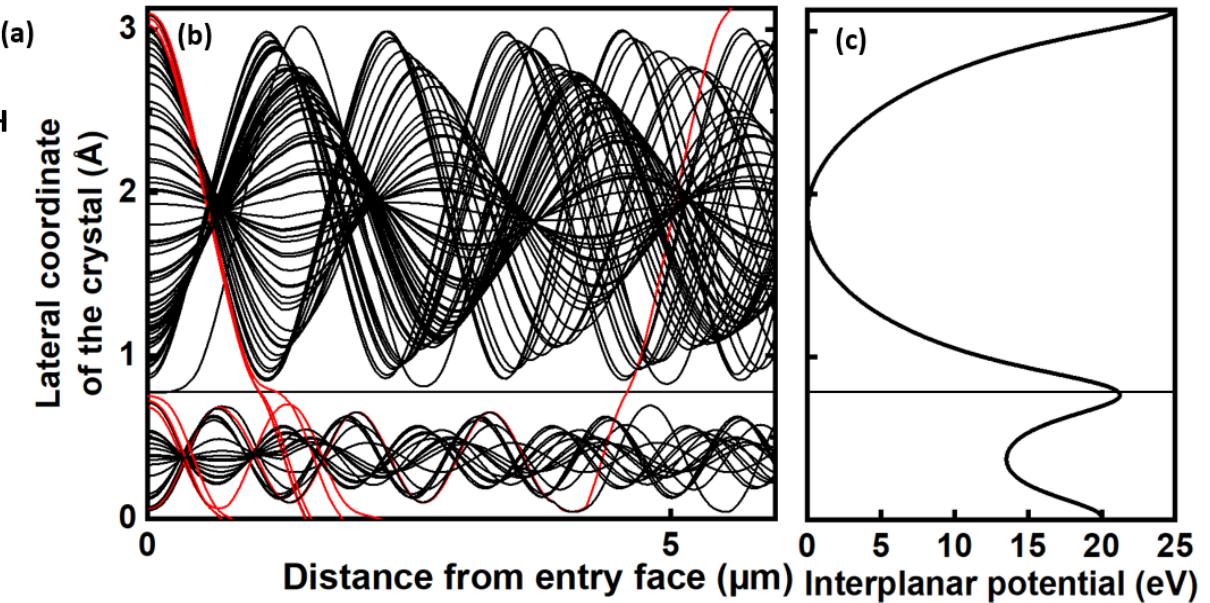
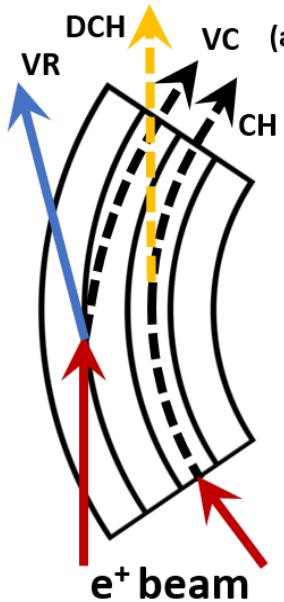
Guidi, V., et al.,, 2009. *Journal of Physics D Applied Physics* 42(18).
 Germogli, G., NIM B, 2015. 355: p. 81-85



Crystal label: BC-Si-QMO*

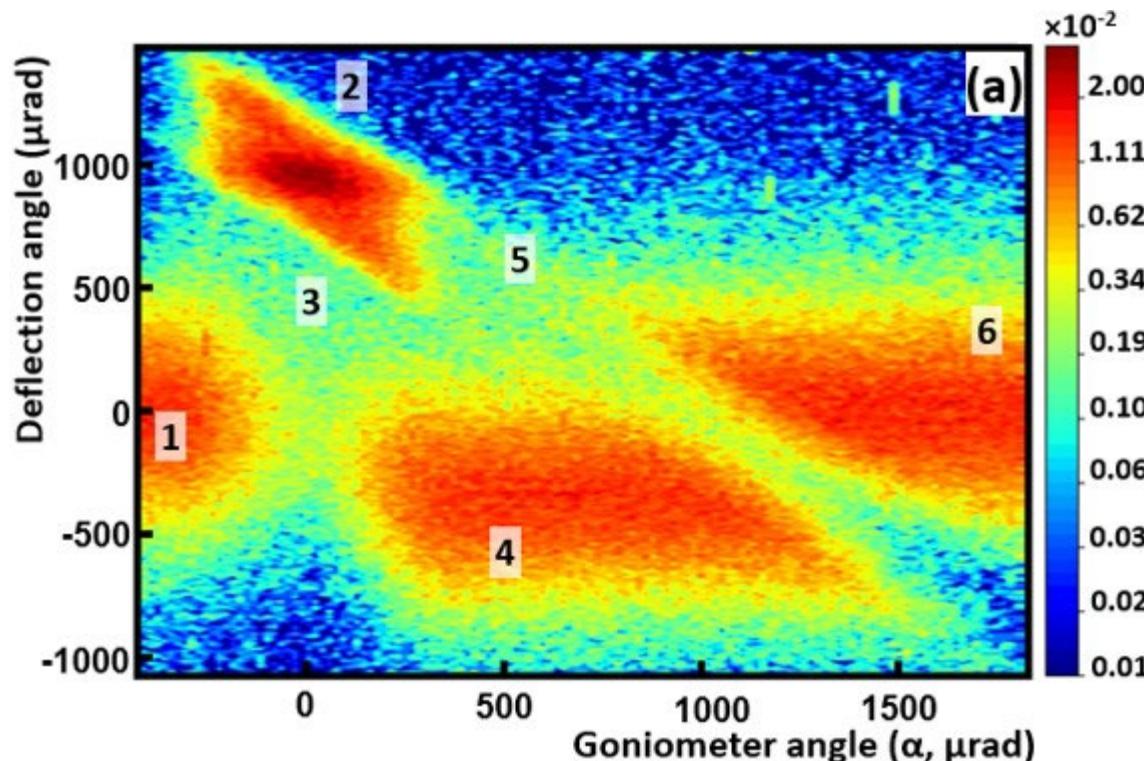
Thickness along the beam: $29.9 \pm 0.1 \mu\text{m}$ Bent planes, exploiting quasimosaic effect (111)

Bending angle: $970 \pm 10 \mu\text{rad}$



*Crystal available from
a previous project @

Experimental results on beam steering of 530 MeV positrons



Mazzolari, A., Backe, H., Bandiera, L., et al., (2024)
arXiv:2404.08459

**TECHNO-CLS MILESTONE:
First high-efficient deflection of
sub-GeV positron worldwide !!!**

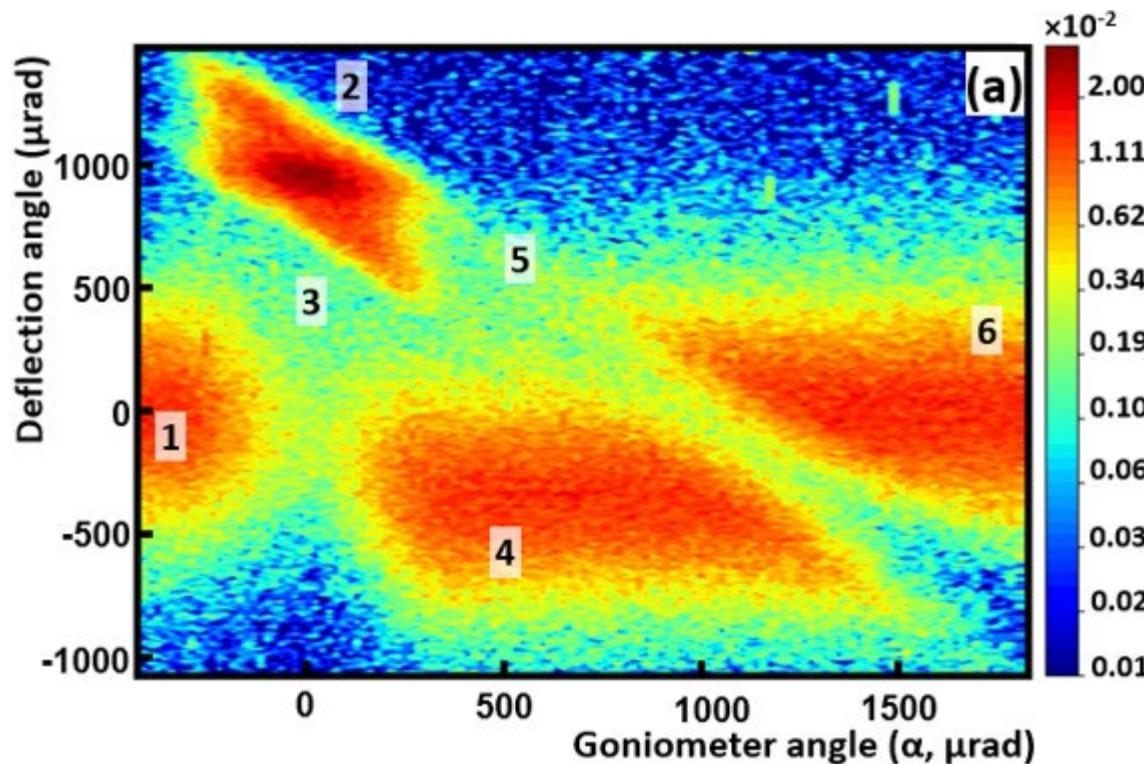
Fallout in :

- Crystal-Light-Source
- Channeling based technologies
- Accelerator technologies: for beam steering, extraction, focusing..

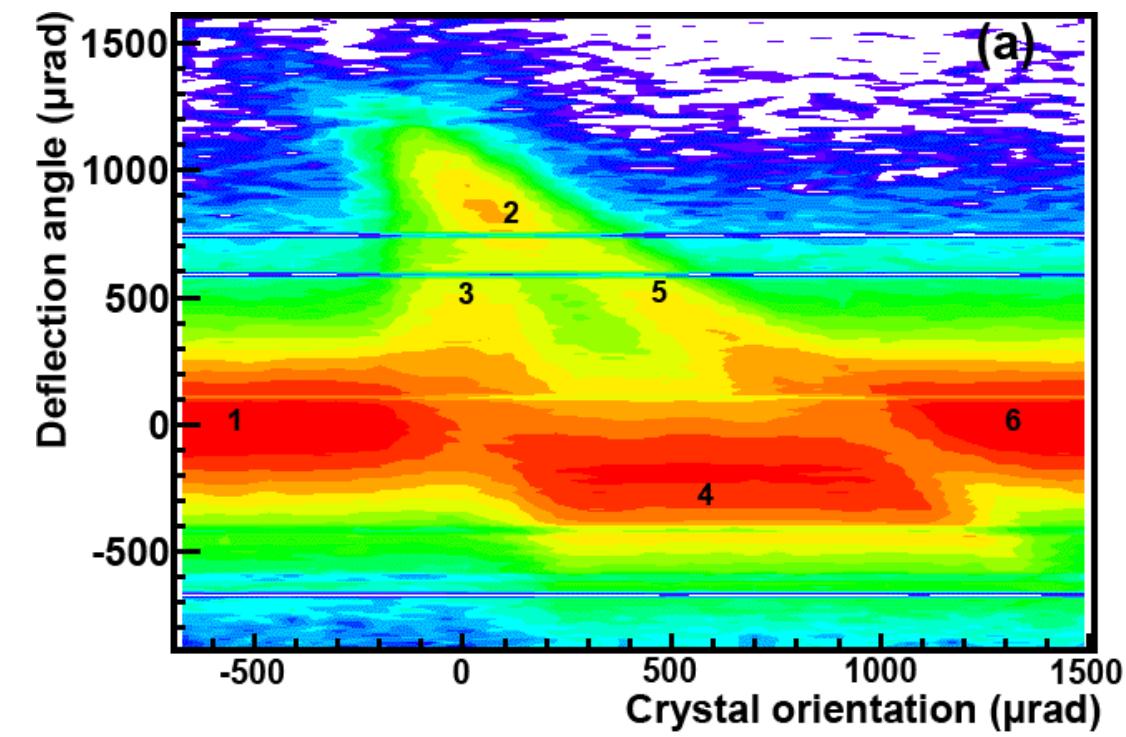
Open access paper on arXiv
Submitted to Phys. Rev. Lett.

530 MeV positrons* vs 855 MeV electrons**

Angular scan for deflected beam distribution: (1) and (6) nonchanneling regime; (2) channeling; (3) dechanneling; (4) volume reflection; and (5) volume capture.



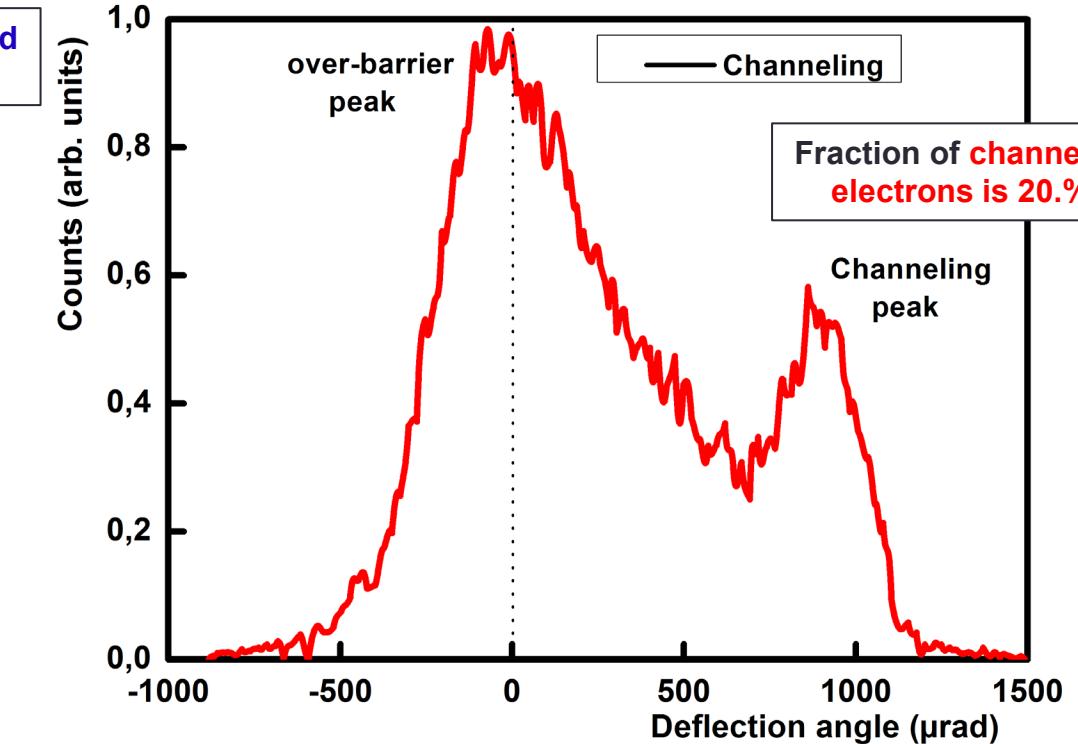
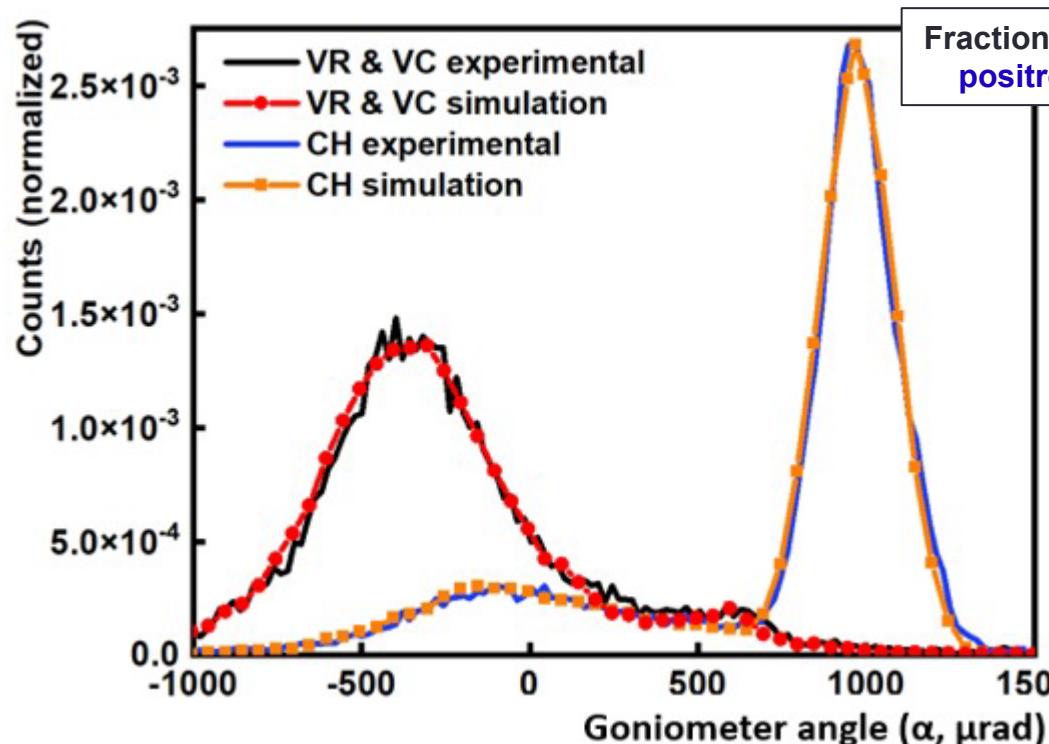
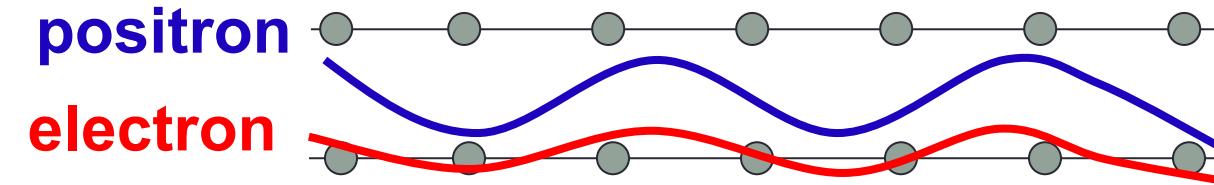
*Mazzolari, A., Backe, H., Bandiera, L., et al., (2024)
arXiv:2404.08459



**Mazzolari A., Bagli E., Bandiera L., et al.,
Phys. Rev. Lett. 112 (2014) 135503

Channeling efficiency e+ vs e-

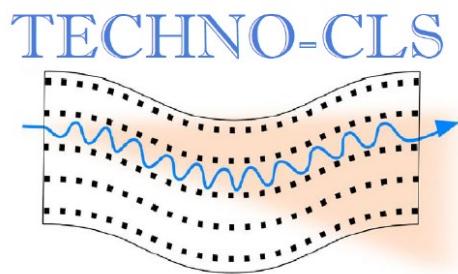
Advantage of positrons for CLS → higher channeling efficiency!



Future experiments with the Positron beam line

- Deflection of positrons (✓)
- Channeling radiation with positrons / Tagging of channeling radiation
- Characterization of Undulator crystals
- Dechanneling length measurements
- Undulator radiation with periodically bent crystals

Thanks for your attention



Horizon Europe EIC-Pathfinder Project
TECHNO-CLS: "Emerging technologies for
crystal-based gamma-ray light sources"



University of
Kent



Istituto Nazionale di Fisica Nucleare



UNIVERSITÀ
DEGLI STUDI
DI PADOVA

JOHANNES GUTENBERG
UNIVERSITÄT MAINZ



Beam spot size and divergence @crystal chamber

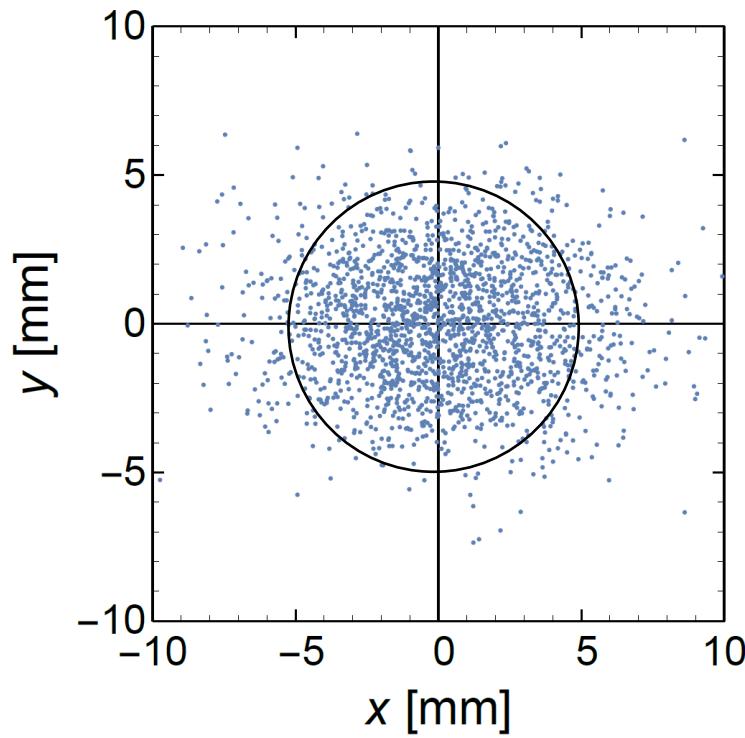
$$\Delta p/p = \pm 1 \cdot 10^{-3} \quad (=) \quad 1\text{MeV}/500\text{MeV}$$

$$\theta_{Positrons} \sim 0.8/\gamma$$

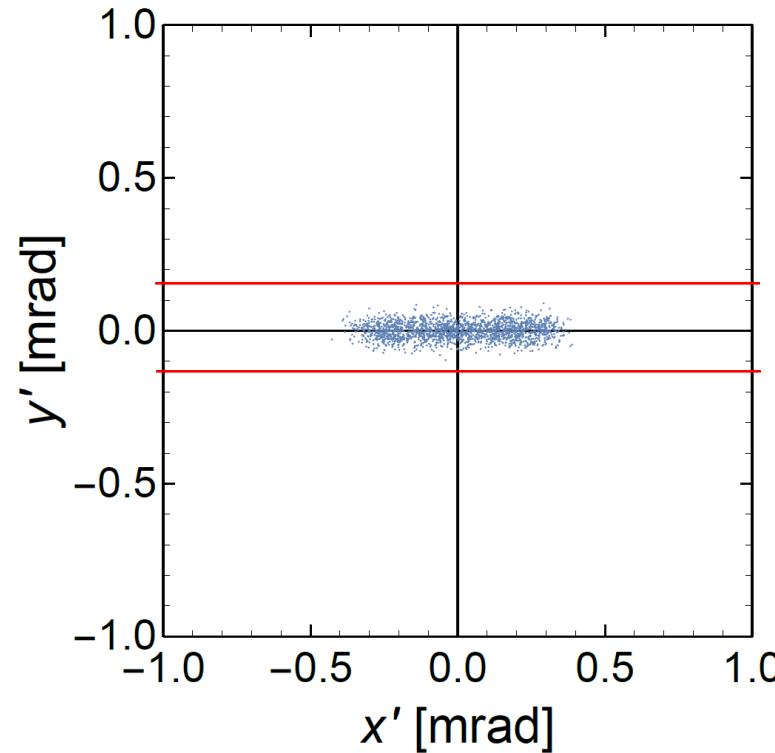
$$\frac{\theta_{Scat}}{2} = 0.56\text{mrad}$$

10 μm W

Beam spot size



Divergence

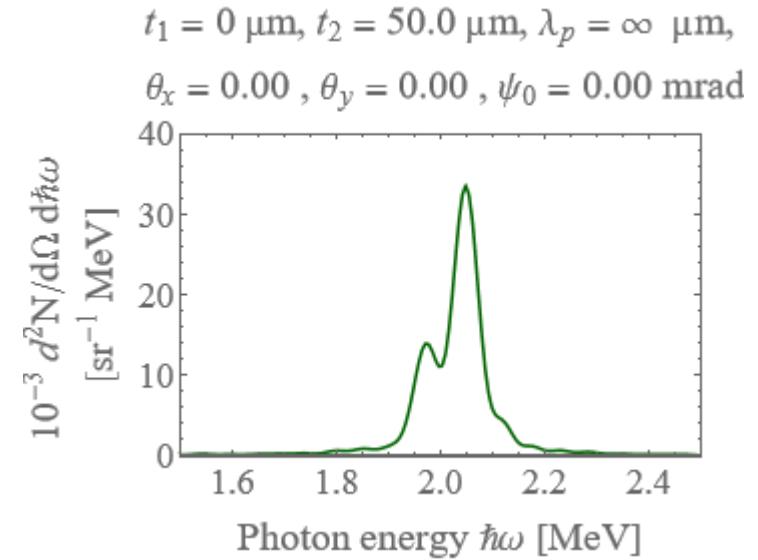


85% accepted in a diameter of 10 mm

Count rate estimation for channeling radiation

Calculation H. Backe et al., arXiv:2404.15376

- Positron rate: $\sim 2 \cdot 10^4$ Positrons/s
- Reduction of beam spot size 2mm
→ 5000 Positrons/s
- Solid angle $3 \cdot 10^{-7}$ sr
(d=4mm, Distance 6m)
- Integral Channeling photons $\sim 3000 / (e^+ \text{ sr})$

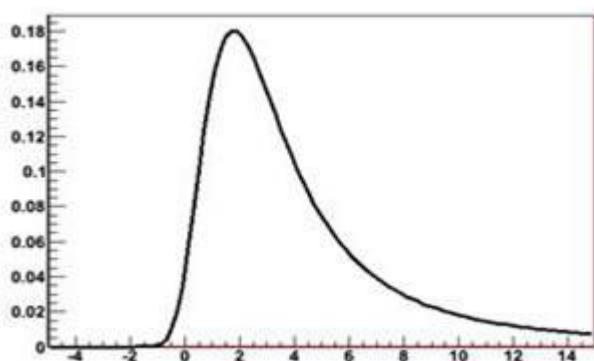
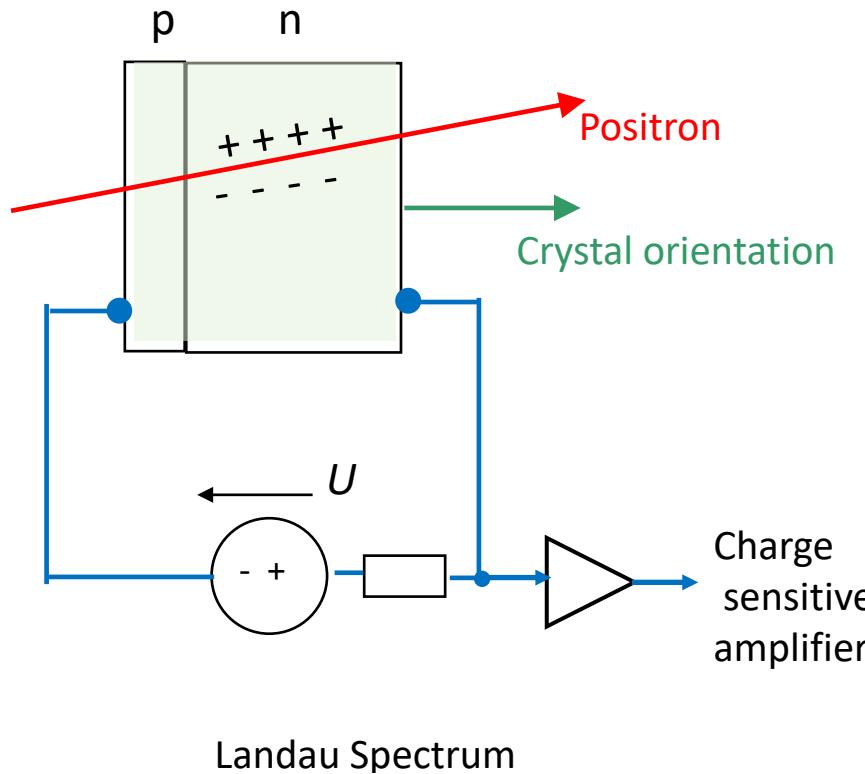


$$\text{Total Count Rate} = \text{Photons}/(e^+ \text{ sr}) \cdot \text{Solid angle} \cdot \text{Positrons/s}$$

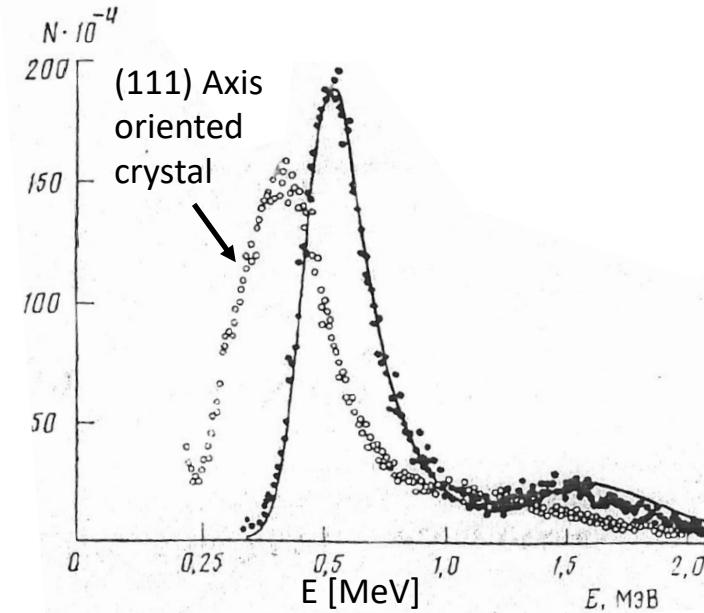
$$= 3000 / (e^+ \text{ sr}) \cdot 3 \cdot 10^{-7} \text{ sr} \cdot 5000 e^+/\text{s}$$

~ 5/s

Dechanneling length measurement with Si-crystal-detector



Ionization loss is different
for channeled and
non channeled particle

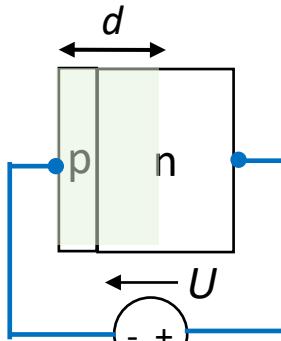


Ionization loss of 1200 MeV positrons
in $160\mu\text{m}$ Si

D.I. Adeishvili, et al.
Journal of Nuclear Physics 48 (1988) 38.

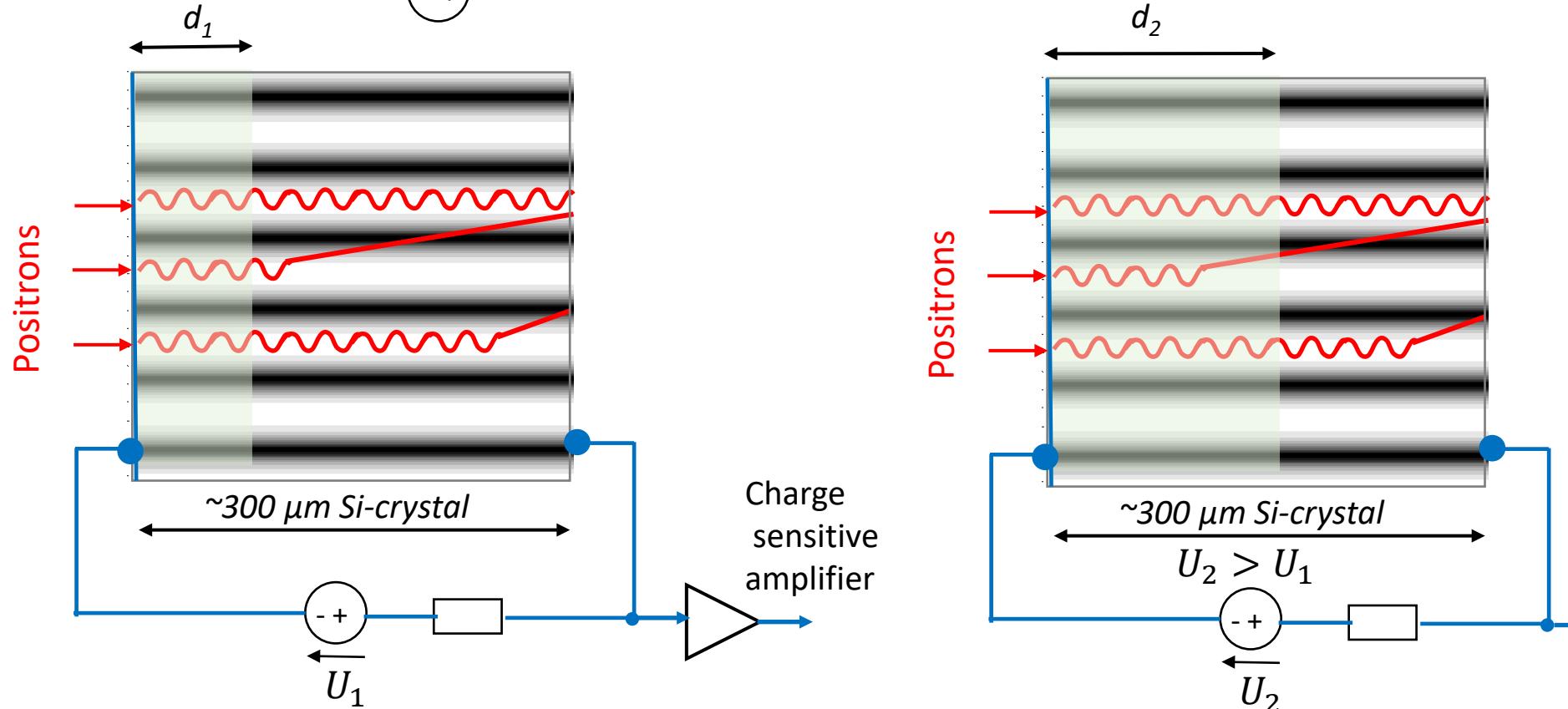
Ionization loss measurements for different detector voltages

A.V. Shchagin et al,
arXiv:2211.01913



$$d = \sqrt{(U + V) \frac{2\epsilon\epsilon_0}{eN}}$$

d: depletion width
U: external voltage
N: doping concentration
V: junction potential $\sim 0.6V$



Signal height of detector \sim produced charge in depletion layer